Ver 1.1

Radiation-Hardened FPGA

Datasheet

Part Number: BQVR300RH





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		Chapter		
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1. Features

- 0.25 μm 5-layer epitaxial process
- •GJB597A-1996 CLASS B \ CAST C
- •Radiation hardened FPGAs for space and satellite Applications
- •Guaranteed over the full military temperature range(-55 °C to +125 °C)
- ●Fast, high-density
 - Field-Programmable Gate Arrays
 - -Densities of 322,970 system gates
 - -System performance up to 200 MHz
 - -66-MHz PCI Compliant
 - -Hot-swappable for Compact PCI
- ●Multi-standard SelectIOTM interfaces -16 high-performance interface

standards

-Connects directly to ZBTRAM devices

- Built-in clock-management circuitry
 Four dedicated delay-locked loops (DLLs) for advanced clock control
 Four primary low-skew global clock distribution nets, plus 24 secondary local clock nets
- Hierarchical memory system
 LUTs configurable as 16-bit RAM,
 32-bit RAM, 16-bit dual-ported RAM,
 or 16-bit Shift Register
 Configurable synchronous
 dual-ported 4k-bit RAMs
 Fast interfaces to external
 high-performance RAMs



•Flexible architecture that balances speed and density

- -Dedicated carry logic for
- high-speed arithmetic
- -Cascade chain for wide-input functions
- -Abundant registers/latches with
- clock enable, and dual

synchronous/asynchronous set and reset

- -Internal 3-state bussing
- -IEEE 1149.1 boundary-scan logic
- -Die-temperature sensor diode
- •Supported by Xilinx develop tools -Complete support for ISE10.1
 - Complete support for PC with Windows XP system
- •SRAM-based in-system configuration
 - -Unlimited re-programmability
 - -Four programming modes
- •Guaranteed total ionizing dose to 100K Rad(Si)
- •SEL immune to LET >75 MeV·cm²/mg
- •SEU threshold value is 15 MeV·cm²/mg (10% saturation cross section)

2. General Description

The BQVR300RH delivers high-performance, high-capacity programmable logic solutions. Dramatic increases in silicon efficiency result from optimizing the new architecture for place-and-route efficiency and exploiting an aggressive 5-layer-metal 0.25um CMOS process. These advances make BQVR300RH powerful and flexible alternatives to mask-programmed gate arrays. The BQVR300RH comprises sorts of resources shown in Table1.

Building on experience gained from previous generations of FPGA, the BQVR300RH represents a revolutionary step forward in programmable logic design. Combining a wide variety of programmable system features, a rich hierarchy of fast, flexible interconnect resources, and advanced process technology, the BQVR300RH a high-speed and high-capacity programmable logic solution that enhances design flexibility while reducing time-to-market.

The anti-radiation capacity of BQVR300RH is as follows:

- Total Ionizing Dose: no less than $1.0 \times 10^5 \operatorname{rad}(\operatorname{Si})^1$
- LET of Single Event Latch-up: no less than 75 $MeV \cdot cm^2/mg$
- LET of Single Event Latch-up: no less than 15 MeV·cm²/mg (10% saturation cross section)

If a user first start BQVR300RH, some important information should be noticed, see in appendix II.

Device	C. A C. A.	CLB Array	Logic Cells	Maximum	Block RAM	Maximum
Device	System Gates	CLD Affay		Available I/O	Bits	SelectRAM+TM Bits
BQVR300RH	322,970	32x48	6,912	162	65,536	98,304

Table 1: BQVR300RH Field-Programmable Gate Array resources

Note:

1. As device characteristics are changed during Total Ionizing Dose test, the device may fail the power-on. The devices should only power on for just one time during the radiation experiment and be kept in a state of none configuration. After 1.0×10^5 rad(si) radiation the devices should be directly put under the temperature of 100 centigrade for 168 hours and then the function of the device can be tested.

3. BQVR300RH Architecture

BQVR300RH feature a flexible, regular architecture that comprises an array of configurable logic blocks (CLBs) surrounded by programmable input/output blocks (IOBs), all interconnected by a rich hierarchy of fast, versatile routing resources. The abundance of routing resources permits the BQVR300RH to accommodate even the largest and most complex designs.

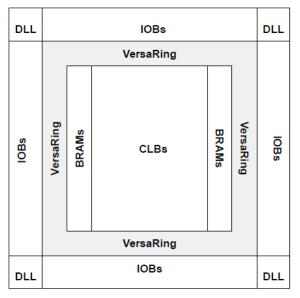


Figure 1: Virtex Architecture Overview

The BQVR300RH user-programmable gate array, shown in Figure 1, comprises two major configurable elements: configurable logic blocks (CLBs) and input/output blocks(IOBs).

- CLBs provide the functional elements for constructing logic
- IOBs provide the interface between the package pins and the CLBs

CLBs interconnect through a general routing matrix (GRM). The GRM comprises an array of routing switches located at the intersections of horizontal and vertical routing channels. Each CLB nests into a VersaBlock that also provides local routing resources to connect the CLB to the GRM. The VersaRing I/O interface provides additional routing resources around the periphery of the device. This routing improves I/O routability and facilitates pin locking. The BQVR300RH architecture also includes the following circuits that connect to the GRM.

- Dedicated block memories of 4096 bits each
- · Clock DLLs for clock-distribution delay compensation and clock domain



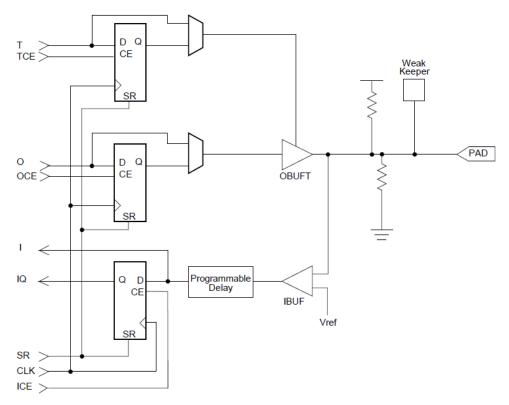
control

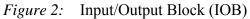
• 3-State buffers (BUFTs) associated with each CLB that drive dedicated segmentable horizontal routing resources

Values stored in static memory cells control the configurable logic elements and interconnect resources. These values load into the memory cells on power-up, and can reload if necessary to change the function of the device.

3.1Input/Output Block

The BQVR300RH IOB, Figure 2, that support a wide variety of I/O signalling standards, see Table 2.The three IOB storage elements function either as edge-triggered D-type flip-flops or as level sensitive latches. Each IOB has a clock signal (CLK) shared by the three flip-flops and independent clock enable signals for each flip-flop. In addition to the CLK and CE control signals, the three flip-flops share a Set/Reset (SR). For each flip-flop, this signal can be independently configured as a synchronous Set, a synchronous Reset, an asynchronous Preset, or an asynchronous Clear.





The output buffer and all of the IOB control signals have independent polarity controls.



All pads are protected against damage from electrostatic discharge (ESD) and from over-voltage transients. Two forms of over-voltage protection are provided, one that permits 5 V compliance, and one that does not. For 5 V compliance, a Zener-like structure connected to ground turns on when the output rises to approximately 6.5 V. When PCI 3.3 V compliance is required, a conventional clamp diode is connected to the output supply voltage, VCCO. Optional pull-up and pull-down resistors and an optional weak-keeper circuit are attached to each pad. Prior to configuration, all pins not involved in configuration are forced into their high-impedance state. The pull-down resistors and the weak-keeper circuits are inactive, but inputs can optionally be pulled up. The activation of pull-up resistors prior to configuration is controlled on a global basis by the configuration mode pins. If the pull-up resistors are not activated, all the pins will float. Consequently, external pull-up or pull-down resistors must be provided on pins required to be at a well-defined logic level prior to configuration. All BQVR300RH IOBs support IEEE 1149.1-compatible boundary scan testing.

I/O Standard	Input Reference	Output Source	Board	5V Tolerant
	Voltage (VREF)	Voltage	Termination	
		(VCCO)	Voltage (VTT)	
LVTTL 2 – 24	N/A	3.3	N/A	Yes
mA				
LVCMOS2	N/A	2.5	N/A	Yes
PCI, 5 V	N/A	3.3	N/A	Yes
PCI, 3.3 V	N/A	3.3	N/A	No
GTL	0.8	N/A	1.2	No
GTL+	1.0	N/A	1.5	No
HSTL Class I	0.75	1.5	0.75	No
HSTL Class III	0.9	1.5	1.5	No
HSTL Class IV	0.9	1.5	1.5	No
SSTL3 Class I	1.5	3.3	1.5	No
&II				
SSTL2 Class I &	1.25	2.5	1.25	No
II				
СТТ	1.5	3.3	1.5	No

Table 2: Supported Select I/O Standards

		京微电子技术研究 ng Microelectronics Technology In		
AGP	1.32	3.3	N/A	No

Input Path

A buffer In the BQVR300RH IOB input path routes the input signal either directly to internal logic or through an optional input flip-flop.

An optional delay element at the D-input of this flip-flop eliminates pad-to-pad hold time. The delay is matched to the internal clock-distribution delay of the FPGA, and when used, assures that the pad-to-pad hold time is zero.

Each input buffer can be configured to conform to any of the low-voltage signalling standards supported. In some of these standards the input buffer utilizes a user-supplied threshold voltage, VREF. The need to supply VREF imposes constraints on which standards can used in close proximity to each other. See I/O Banking, page 6. There are optional pull-up and pull-down resistors at each input for use after configuration. Their value is in the range 20 k Ω – 70 k Ω .

Output Path

The output path includes a 3-state output buffer that drives the output signal onto the pad. The output signal can be routed to the buffer directly from the internal logic or through an optional IOB output flip-flop.

The 3-state control of the output can also be routed directly from the internal logic or through a flip-flip that provides synchronous enable and disable.

Each output driver can be individually programmed for a wide range of low-voltage signalling standards. Each output buffer can source up to 24 mA and sink up to 48mA. Drive strength and slew rate controls minimize bus transients.

In most signalling standards, the output High voltage depends on an externally supplied VCCO voltage. The need to supply VCCO imposes constraints on which standards can be used in close proximity to each other. See I/O Banking, page 6.

An optional weak-keeper circuit is connected to each output. When selected, the circuit monitors the voltage on the pad and weakly drives the pin High or Low to match the input signal. If the pin is connected to a multiple-source signal, the weak keeper holds the signal in its last state if all drivers are disabled. Maintaining a valid logic level in this way eliminates bus chatter.

Because the weak-keeper circuit uses the IOB input buffer to monitor the input level, an appropriate VREF voltage must be provided if the signalling standard



requires one. The provision of this voltage must comply with the I/O banking rules.

I/O Banking

Some of the I/O standards described above require VCCO and/or VREF voltages. These voltages externally and connected to device pins that serve groups of IOBs, called banks. Consequently, restrictions exist about which I/O standards can be combined within a given bank.

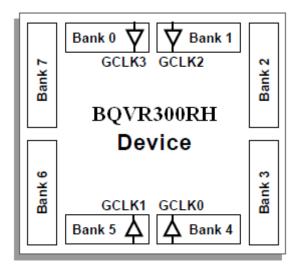


Figure 3: BQVR300RH I/O Banks

Eight I/O banks result from separating each edge of the FPGA into two banks, as shown in Figure 3. Each bank has multiple VCCO pins, all of which must be connected to the same voltage. This voltage is determined by the output standards in use.

Within a bank, output standards can be mixed only if they use the same VCCO. Compatible standards are shown in Table 3. GTL and GTL+ appear under all voltages because their open-drain outputs do not depend on VCCO.

VCCO	Compatible Standards
3.3 V	PCI, LVTTL, SSTL3 I, SSTL3 II, CTT, AGP, GTL, GTL+
2.5 V	SSTL2 I, SSTL2 II, LVCMOS2, GTL, GTL+
1.5 V	HSTL I, HSTL III, HSTL IV, GTL, GTL+

Table 3: Compatible Output Standards

Some input standards require a user-supplied threshold voltage, VREF. In this case, certain user-I/O pins are automatically configured as inputs for the VREF voltage. Approximately one in six of the I/O pins in the bank assume this role.



The VREF pins within a bank are interconnected internally and consequently only one VREF voltage can be used within each bank. All VREF pins in the bank, however, must be connected to the external voltage source for correct operation.

Within a bank, inputs that require VREF can be mixed with those that do not. However, only one VREF voltage can be used within a bank. Input buffers that use VREF are not 5 V tolerant. LVTTL, LVCMOS2, and PCI 33 MHz 5 V, are 5 V tolerant.

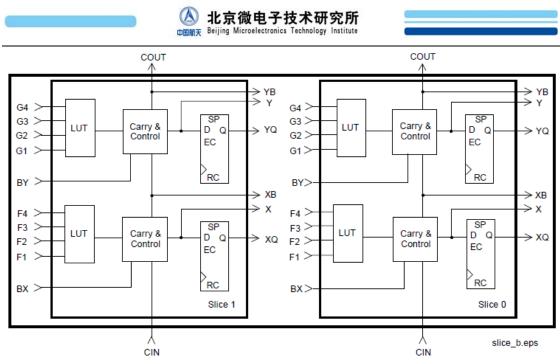
The VCCO and VREF pins for each bank appear in the device Pinout tables.

Within a given package, the number of VREF and VCCO pins can vary depending on the size of device. In larger devices, more I/O pins convert to VREF pins. Since these are always a superset of the VREF pins used for smaller devices, it is possible to design a PCB that permits migration to a larger device if necessary. All the VREF pins for the largest device anticipated must be connected to the VREF voltage, and not used for I/O.

In BQVR300RH, all VCCO pins are bonded together internally, and consequently the same VCCO voltage must be connected to all of them, the VREF pins remain internally connected as eight banks, and can be used as described previously.

3.2Configurable Logic Block

The basic building block of the BQVR300RH CLB is the logic cell (LC). An LC includes a 4-input function generator, carry logic, and a storage element. The output from the function generator in each LC drives both the CLB output and the D input of the flip-flop. Each CLB contains four LCs, organized in two similar slices, as shown in Figure 4.



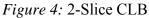


Figure 5 shows a more detailed view of a single slice. In addition to the four basic LCs, the CLB contains logic that combines function generators to provide functions of five or six inputs. Consequently, when estimating the number of system gates provided by a given device, each CLB counts as 4.5 LCs.

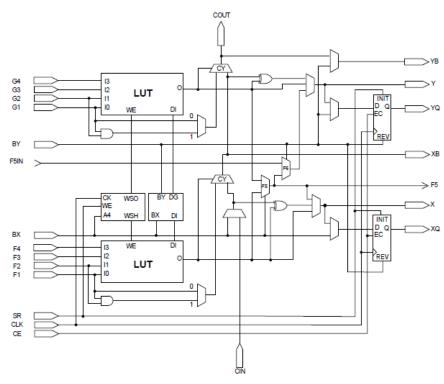


Figure 5: Detailed View of Slice

Look-Up Tables

BQVR300RH function generators are implemented as 4-input look-up tables



(LUTs). In addition to operating as a function generator, each LUT can provide a 16×1 -bit synchronous RAM. Furthermore, the two LUTs within a slice can be combined to create a 16×2 -bit or 32×1 -bit synchronous RAM, or a 16×1 -bit dual-port synchronous RAM.

The BQVR300RH LUT can also provide a 16-bit shift register that is ideal for capturing high-speed or burst-mode data. This mode can also be used to store data in applications such as Digital Signal Processing.

Storage Elements

The storage elements in the slice can be configured either as edge-triggered D-type flip-flops or as level-sensitive latches. The D inputs can be driven either by the function generators within the slice or directly from slice inputs, bypassing the function generators.

In addition to Clock and Clock Enable signals, each Slice has synchronous set and reset signals (SR and BY). SR forces a storage element into the initialization state specified for it in the configuration. BY forces it into the opposite state. Alternatively, these signals can be configured to operate asynchronously. All of the control signals are independently invertible, and are shared by the two flip-flops within the slice.

Additional Logic

The F5 multiplexer in each slice combines the function generator outputs. This combination provides either a function generator that can implement any 5-input function, a 4:1 multiplexer, or selected functions of up to nine inputs. Similarly, the F6 multiplexer combines the outputs of all four function generators in the CLB by selecting one of the F5-multiplexer outputs. This permits the implementation of any 6-input function, an 8:1 multiplexer, or selected functions of up to 19 inputs.

Each CLB has four direct feedthrough paths, one per LC. These paths provide extra data input lines or additional local routing that does not consume logic resources.

Arithmetic Logic

Dedicated carry logic provides fast arithmetic carry capability for high-speed arithmetic functions. The BQVR300RH CLB supports two separate carry chains, one per Slice. The height of the carry chains is two bits per CLB.

The arithmetic logic includes an XOR gate that allows a 1-bit full adder to be implemented within an LC. In addition, a dedicated AND gate improves the



efficiency of multiplier implementation.

The dedicated carry path can also be used to cascade function generators for implementing wide logic functions.

BUFTs

Each CLB contains two 3-state drivers (BUFTs) that can drive on-chip busses. See Dedicated Routing, page 11.

Each BUFT has an independent 3-state control pin and an independent input pin.

3.3Block SelectRAM

BQVR300RH FPGAs incorporate several large Block SelectRAM memories. These complement the distributed LUT SelectRAMs that provide shallow RAM structures implemented in CLBs.

Block SelectRAM memory blocks are organized in columns. BQVR300RH contains two such columns, one along each vertical edge. These columns extend the full height of the chip. Each memory block is four CLBs high, and consequently, a device contains 16 memory blocks.

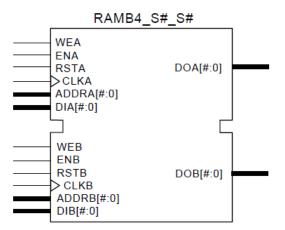


Figure 6: Dual-Port Block SelectRAM

Each Block SelectRAM cell, as illustrated in Figure 6, is a fully synchronous dual-ported 4096-bit RAM with independent control signals for each port. The data widths of the two ports can be configured independently, providing built-in bus-width conversion.

Table 4: Block SelectRAM Port Aspect Ratios

Width	Depth	ADDR Bus	Data Bus

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1	4096	ADDR<11:0>	DATA<0>	
2	2048	ADDR<10:0>	DATA<1:0>	
4	1024	ADDR<9:0>	DATA<3:0>	
8	512	ADDR<8:0>	DATA<7:0>	
16	256	ADDR<7:0>	DATA<15:0>	

Table 4 shows the depth and width aspect ratios for the Block SelectRAM. The Block SelectRAM also includes dedicated routing to provide an efficient interface with both CLBs and other Block SelectRAMs.

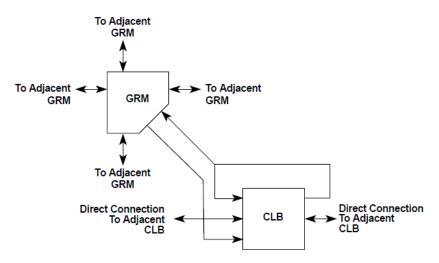
3.4Programmable Routing Matrix

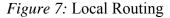
It is the longest delay path that limits the speed of any worst-case design. Consequently, the BQVR300RH routing architecture and its place-and-route software were defined in a single optimization process. This joint optimization minimizes long-path delays, and consequently, yields the best system performance.

The joint optimization also reduces design compilation times because the architecture is software-friendly. Design cycles are correspondingly reduced due to shorter design iteration times.

Local Routing

The VersaBlock provides local routing resources, as shown in Figure 7, providing the following three types of connections.





• Interconnections among the LUTs, flip-flops, and GRM



• Internal CLB feedback paths that provide high-speed connections to LUTs within the same CLB, chaining them together with minimal routing delay

• Direct paths that provide high-speed connections between horizontally adjacent CLBs, eliminating the delay of the GRM.

General Purpose Routing

Most BQVR300RH signals are routed on the general purpose routing, and consequently, the majority of interconnect resources are associated with this level of the routing hierarchy.

The general routing resources are located in horizontal and vertical routing channels associated with the rows and columns CLBs. The general-purpose routing resources are listed below.

• Adjacent to each CLB is a General Routing Matrix (GRM). The GRM is the switch matrix through which horizontal and vertical routing resources connect, and is also the means by which the CLB gains access to the general purpose routing.

• 24 single-length lines route GRM signals to adjacent GRMs in each of the four directions.

• 72 buffered Hex lines route GRM signals to another GRMs six-blocks away in each one of the four directions. Organized in a staggered pattern, Hex lines can be driven only at their endpoints. Hex-line signals can be accessed either at the endpoints or at the midpoint (three blocks from the source). One third of the Hex lines are bidirectional, while the remaining ones are uni-directional.

Global Routing

Global Routing resources distribute clocks and other signals with very high fanout throughout the device. BQVR300RH devices include two tiers of global routing resources referred to as primary global and secondary local clock routing resources.

• The primary global routing resources are four dedicated global nets with dedicated input pins that are designed to distribute high-fanout clock signals with minimal skew. Each global clock net can drive all CLB, IOB, and block RAM clock pins. The primary global nets can only be driven by global buffers. There are four global buffers, one for each global net.

• 12 Longlines are buffered, bidirectional wires that distribute signals across the



device quickly and efficiently. Vertical Longlines span the full height of the device, and horizontal ones span the full width of the device.

I/O Routing

BQVR300RH devices have additional routing resources around their periphery that form an interface between the CLB array and the IOBs. This additional routing, called the VersaRing, facilitates pin-swapping and pin-locking, such that logic redesigns can adapt to existing PCB layouts. Time-to-market is reduced, since PCBs and other system components can be manufactured while the logic design is still in progress.

Dedicated Routing

Some classes of signal require dedicated routing resources to maximize performance. In the BQVR300RH architecture, dedicated routing resources are provided for two classes of signal.

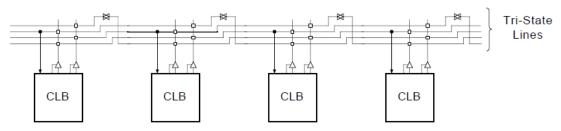


Figure 8: BUFT Connections to Dedicated Horizontal Bus Lines

• Horizontal routing resources are provided for on-chip 3-state busses. Four partitionable bus lines are provided per CLB row, permitting multiple busses within a row, as shown in Figure 8.

• Two dedicated nets per CLB propagate carry signals vertically to the adjacent CLB.

• The secondary local clock routing resources consist of 24 backbone lines, 12 across the top of the chip and 12 across bottom. From these lines, up to 12 unique signals per column can be distributed via the 12 longlines in the column. These secondary resources are more flexible than the primary resources since they are not restricted to routing only to clock pins.

Clock Distribution

BQVR300RH provides high-speed, low-skew clock distribution through the primary global routing resources described above. A typical clock distribution net is shown in Figure 9.

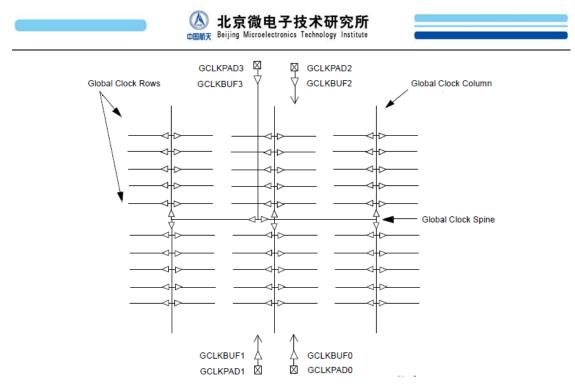


Figure 9: Global Clock Distribution Network

Four global buffers are provided, two at the top center of the device and two at the bottom center. These drive the four primary global nets that in turn drive any clock pin. Four dedicated clock pads are provided, one adjacent to each of the global buffers. The input to the global buffer is selected either from these pads or from signals in the general purpose routing.

3.5Delay-Locked Loop (DLL)

Associated with each global clock input buffer is a fully digital Delay-Locked Loop (DLL) that can eliminate skew between the clock input pad and internal clock-input pins throughout the device. Each DLL can drive two global clocknetworks. The DLL monitors the input clock and the distributed clock, and automatically adjusts a clock delay element.

Clock edges reach internal flip-flops one to four clock periods after they arrive at the input. This closed-loop system effectively eliminates clock-distribution delay by ensuring that clock edges arrive at internal flip-flops in synchronism with clock edges arriving at the input.

In addition to eliminating clock-distribution delay, the DLL provides advanced control of multiple clock domains. The DLL provides four quadrature phases of the source clock, can double the clock, or divide the clock by 1.5, 2, 2.5, 3, 4, 5, 8, or 16.

The DLL also operates as a clock mirror. By driving the output from a DLL

off-chip and then back on again, the DLL can be used to de-skew a board level clock among multiple BQVR300RH devices.

In order to guarantee that the system clock is operating correctly prior to the FPGA starting up after configuration, the DLL can delay the completion of the configuration process until after it has achieved lock.

3.6Boundary Scan

BQVR300RH devices support all the mandatory boundary-scan instructions specified in the IEEE standard 1149.1. A Test Access Port (TAP) and registers are provided that implement the EXTEST, INTEST, SAMPLE/PRELOAD, BYPASS, IDCODE, USERCODE, and HIGHZ instructions. The TAP also supports two internal scan chains and configuration/readback of the device. The TAP uses dedicated package pins that always operate using LVTTL. For TDO to operate using LVTTL, the VCCO for Bank 2 should be 3.3 V.

Otherwise, TDO switches rail-to-rail between ground and VCCO. Boundary-scan operation is independent of individual IOB configurations, and unaffected by package type. All IOBs, including un-bonded ones, are treated as independent 3-state bidirectional pins in a single scan chain. Retention of the bidirectional test capability after configuration facilitates the testing of external interconnections.

Table 5 lists the boundary-scan instructions supported in BQVR300RH FPGAs. Internal signals can be captured during EXTEST by connecting them to un-bonded or unused IOBs. They can also be connected to the unused outputs of IOBs defined as unidirectional input pins.

Boundary-Scan	Binary	Description
Command	Code(4:0)	
EXTEST	00000	Enables boundary-scan
		EXTEST operation
SAMPLE/PRELOAD	00001	Enables boundary-scan
		SAMPLE/PRELOAD
		operation
USER 1	00010	Access user-defined

Table 5: Boundary Scan Instructions

中国航天	北京微电子技术 Beijing Microelectronics Technolo	研究所 ogy Institute
		register 1
USER 2	00011	Access user-defined
		register 2
CFG_OUT	00100	Access the configuration
		bus for read operations.
CFG_IN	00101	Access the configuration
		bus for write operations.
INTEST	00111	Enables boundary-scan
		INTEST operation
USERCODE	01000	Enables shifting out
		USER code
IDCODE	01001	Enables shifting out of ID
		Code
HIGHZ	01010	3-states output pins while
		enabling the Bypass
		Register
JSTART	01100	Clock the start-up
		sequence when
		StartupClk is TCK
BYPASS	11111	Enables BYPASS
RESERVED	All other	reserved
	codes	instructions

Before the device is configured, all instructions except USER1 and USER2 are available. After configuration, all instructions are available. During configuration, it is recommended that those operations using the boundary-scan register (SAMPLE/PRELOAD, INTEST, EXTEST) not be performed.

In addition to the test instructions outlined above, the boundary-scan circuitry can be used to configure the FPGA, and also to read back the configuration data.

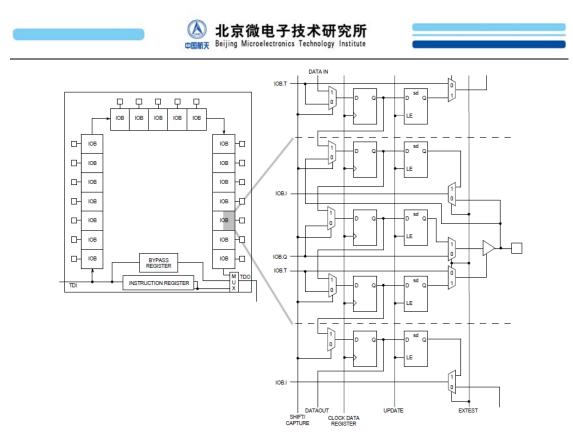


Figure 10: Boundary Scan Logic

Figure 10 is a diagram of the BQVR300RH boundary scan logic. It includes three bits of Data Register per IOB, the IEEE 1149.1 Test Access Port controller, and the Instruction Register with decodes.

Instruction Set

The boundary scan instruction set also includes instructions to configure the device and read back configuration data (CFG_IN, CFG_OUT, and JSTART). The complete instruction set is coded as shown in Table 5.

Data Registers

The primary data register is the boundary scan register. For each IOB pin in the FPGA, bonded or not, it includes three bits for In, Out, and 3-State Control. Non-IOB pins have appropriate partial bit population if input-only or output-only.

Each EXTEST CAPTURED-OR state captures all In, Out, and 3-state pins.

The other standard data register is the single flip-flop BYPASS register. It synchronizes data being passed through the FPGA to the next downstream boundary scan device.

The FPGA supports up to two additional internal scan chains that can be specified using the BSCAN macro. The macro provides two user pins (SEL1 and SEL2) which are decodes of the USER1 and USER2 instructions respectively.



For these instructions, two corresponding pins (TDO1 and TDO2) allow user scan data to be shifted out of TDO. Likewise, there are individual clock pins (DRCK1 and DRCK2) for each user register. There is a common input pin (TDI) and shared output pins that represent the state of the TAP controller (RESET, SHIFT, and UPDATE).

Bit Sequence

The order within each IOB is: In, Out, 3-State. The input-only pins contribute only the In bit to the boundary scan I/O data register, while the output-only pins contributes all three bits.

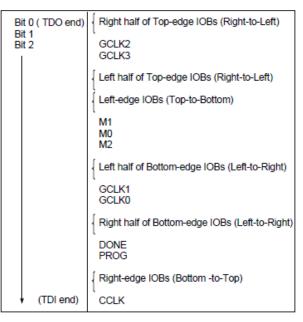


Figure 11: Boundary Scan Bit Sequence

From a cavity-up view of the chip (as shown in EPIC), starting in the upper right chip corner, the boundary scan data-register bits are ordered as shown in Figure 11.

Identification Registers

The IDCODE register is supported. By using the IDCODE, the device connected to the JTAG port can be determined. The IDCODE of BQVR300RH is: v0620093

The USERCODE register is supported. By using the USERCODE, a user-programmable identification code can be loaded and shifted out for examination. The identification code is embedded in the bitstream during bitstream generation and is valid only after configuration.

Including Boundary Scan in a Design

Since the boundary scan pins are dedicated, no special element needs to be added



to the design unless an internal data register (USER1 or USER2) is desired.

If an internal data register is used, insert the boundary scan symbol and connect the necessary pins as appropriate.

3.7Development System

BQVR300RH FPGAs are supported by the Xilinx ISE tools. The basic methodology for BQVR300RH design consists of three interrelated steps: design entry, implementation, and verification. Industry-standard tools are used for design entry and simulation (for example, Modelsim), while BMTI provides proprietary architecture-specific tools for implementation.

The development system is integrated under the ISE software, providing designers with a common user interface regardless of their choice of entry and verification tools.

Application programs ranging from schematic capture to Placement and Routing (PAR) can be accessed through the ISE software. The program command sequence is generated prior to execution, and stored for documentation.

Several advanced software features facilitate design. RPMs, for example, are schematic-based macros with relative location constraints to guide their placement. They help ensure optimal implementation of common functions.

For HDL design entry, the ISE provides interfaces to the following synthesis design environments.

- FPGA Express
- XST
- Synplify

For schematic design entry, the ISE provides interfaces to the following schematic-capture design environments.

Third-party vendors support many other environments. A standard interface-file specification, Electronic Design Interchange Format (EDIF), simplifies file transfers into and out of the development system.

BQVR300RH supported by a unified library of standard functions. This library contains over 400 primitives and macros, ranging from 2-input AND gates to 16-bit accumulators, and includes arithmetic functions, comparators, counters, data registers,



decoders, encoders, I/O functions, latches, Boolean functions, multiplexers, shift registers, and barrel shifters.

The "soft macro" portion of the library contains detailed descriptions of common logic functions, but does not contain any partitioning or placement information. The performance of these macros depends, therefore, on the partitioning and placement obtained during implementation.

The design environment supports hierarchical design entry, with high-level schematics that comprise major functional blocks, while lower-level schematics define the logic in these blocks. These hierarchical design elements are automatically combined by the implementation tools. Different design entry tools can be combined within a hierarchical design, thus allowing the most convenient entry method to be used for each portion of the design.

Design Implementation

The place-and-route tools (PAR) automatically provide the implementation flow described in this section. The partitioner takes the EDIF net list for the design and maps the logic into the architectural resources of the FPGA (CLBs and IOBs, for example). The placer then determines the best locations for these blocks based on their interconnections and the desired performance. Finally, the router interconnects the blocks.

The PAR algorithms support fully automatic implementation of most designs. For demanding applications, however, the user can exercise various degrees of control over the process.

User partitioning, placement, and routing information is optionally specified during the design-entry process. The implementation of highly structured designs can benefit greatly from basic floor planning.

The implementation software incorporates timing-driven placement and routing. Designers specify timing requirements along entire paths during design entry.

The timing path analysis routines in PAR then recognize these user-specified requirements and accommodate them.

Timing requirements are entered on a schematic in a form directly relating to the system requirements, such as the targeted clock frequency, or the maximum allowable delay between two registers. In this way, the overall performance of the system along entire signal paths is automatically tailored to user-generated specifications. Specific

timing information for individual nets is unnecessary.

Design Verification

In addition to conventional software simulation, FPGA users can use in-circuit debugging techniques. Because BQVR300RH devices are infinitely reprogrammable, designs can be verified in real time without the need for extensive sets of software simulation vectors.

The development system supports both software simulation and in-circuit debugging techniques. For simulation, the system extracts the post-layout timing information from the design database, and back-annotates this information into the net list for use by the simulator. Alternatively, the user can verify timing-critical portions of the design using the static timing analyzer.

For in-circuit debugging, the development system includes a download and readback cable. This cable connects the FPGA in the target system to a PC or workstation. After downloading the design into the FPGA, the designer can single-step the logic, readback the contents of the flip-flops, and so observe the internal logic state. Simple modifications can be downloaded into the system in a matter of minutes.

4. Configuration

BQVR300RH are configured by loading configuration data into the internal configuration memory. Some of the pins used for this are dedicated configuration pins, while others can be re-used as general purpose inputs and outputs once configuration is complete.

The following are dedicated pins:

- ➢ Mode pins (M2, M1, M0)
- Configuration clock pin (CCLK)
- ➢ PROGRAM pin
- ➢ DONE pin
- ▶ Boundary-scan pins (TDI, TDO, TMS, TCK)

Depending on the configuration mode chosen, CCLK can be an output generated by the FPGA, or it can be generated externally and provided to the FPGA as an input.

Note that some configuration pins can act as outputs. For correct operation, these



pins can require a VCCO of 3.3 V to permit LVTTL operation. All the pins affected are in banks 2 or 3.

After BQVR300RH device is configured, unused IOBs function as 3-state OBUFTs with weak pull downs.

4.1Configuration Modes

BQVR300RH supports the following four configuration modes.

- Slave-serial mode
- ➢ Master-serial mode
- SelectMAP mode
- Boundary-scan mode

The Configuration mode pins (M2, M1, M0) select among these configuration modes with the option in each case of

having the IOB pins either pulled up or left floating prior to configuration. The selection codes are listed in Table 6.

Configuration through the boundary-scan port is always available, independent of the mode selection. Selecting the boundary-scan mode simply turns off the other modes. The three mode pins have internal pull-up resistors, and default to a logic High if left unconnected.

Configuration Mode	M2	M1	M0	CCLK Direction	Data Width	Serial Dout	Configuration Pull-ups
Master-serial mode	0	0	0	Out	1	Yes	No
Boundary-scan mode	1	0	1	N/A	1	No	No
SelectMAP mode	1	1	0	In	8	No	No
Slave-serial mode	1	1	1	In	1	Yes	No
Master-serial mode	1	0	0	Out	1	Yes	Yes
Boundary-scan mode	0	0	1	N/A	1	No	Yes
SelectMAP mode	0	1	0	In	8	No	Yes
Slave-serial mode	0	1	1	In	1	Yes	Yes

Table 6: Configuration Codes



4.2Slave-Serial Mode

In slave-serial mode, the FPGA receives configuration data in bit-serial form from a serial PROM or other source of serial configuration data. The serial bitstream must be setup at the DIN input pin a short time before each rising edge of an externally generated CCLK.

Multiple FPGAs can be daisy-chained for configuration from a single source. After a particular FPGA has been configured, the data for the next device is routed to the DOUT pin. The data on the DOUT pin changes on the rising edge of CCLK.

The change of DOUT on the rising edge of CCLK differs from previous families, but does not cause a problem for mixed configuration chains. This change was made to improve serial configuration rates for BQVR300RH-only chains.

Figure 12 shows a full master/slave system. A BQVR300RH device in slave-serial mode should be connected as shown in the third device from the left.

Slave-serial mode is selected by applying <111> or <011> to the mode pins (M2, M1, M0). A weak pull-up on the mode pins makes slave-serial the default mode if the pins are left unconnected. Figure 13 shows slave-serial configuration timing.

Table 7 provides more detail about the characteristics shown in Figure 13. Configuration must be delayed until the INIT pins of all daisy-chained FPGAs are High.

	Description	Figure References	Symbol	Value	Units
CCLK	DIN setup/hold, slave mode	1/2	TDCC/TCCD	5.0 / 0	ns, min
	DIN setup/hold, master mode	1/2	TDSCK/TCKDS	5.0 / 0	ns, min
	DOUT	3	TCCO	12.0	ns, max
	High time	4	ТССН	5.0	ns, min
	Low time	5	TCCL	5.0	ns, min
	Maximum Frequency		FCC	30	MHz, max
	Frequency Tolerance, master mode with			+45%	
	respect to nominal			-45%	

Table 7: Master/Slave Serial Mode Programming Switching

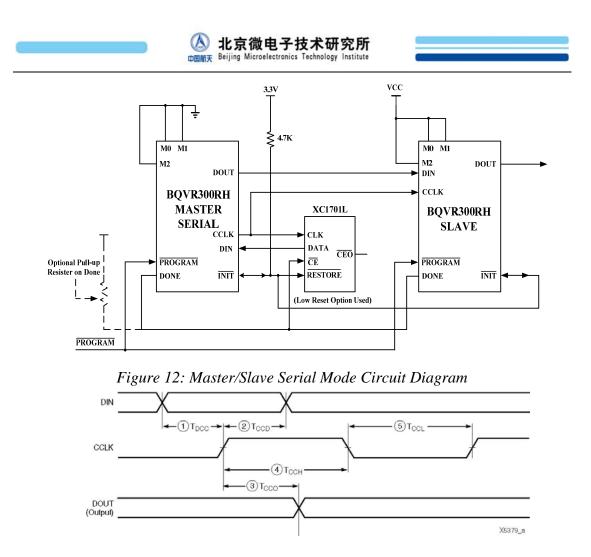


Figure 13: Slave-Serial Mode Programming Switching Characteristics

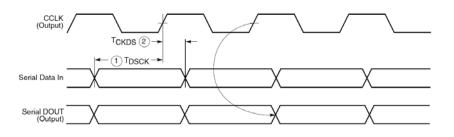


Figure 14: Master-Serial Mode Programming Switching Characteristics

4.3Master-Serial Mode

In master-serial mode, the CCLK output of the FPGA drives a BMTI Serial PROM that feeds bit-serial data to the DIN input. The FPGA accepts this data on each rising CCLK edge. After the FPGA has been loaded, the data for the next device in a daisy-chain is presented on the DOUT pin after the rising CCLK edge.

The interface is identical to slave-serial except that an internal oscillator is used to generate the configuration clock (CCLK). A wide range of frequencies can be



selected for CCLK which always starts at a slow default frequency. Configuration bits then switch CCLK to a higher frequency for the remainder of the configuration. Switching to a lower frequency is prohibited.

The CCLK frequency is set using the ConfigRate option in the bitstream generation software. The maximum CCLK frequency that can be selected is 60 MHz. When selecting a CCLK frequency, ensure that the serial PROM and any CCLK (Output) Serial Data In Serial DOUT (Output) On power-up, the CCLK frequency is 2.5 MHz. This frequency is used until the ConfigRate bits have been loaded when the frequency changes to the selected ConfigRate. Unless a different frequency is specified in the design, the default ConfigRate is 4 MHz. The CCLK frequency set by software options is not actual frequency. The master CCLK frequency has deviations between the test value and the design one, for more information refer to appendix IV.

Figure 12 shows a full master/slave system. In this system, the left-most device operates in master-serial mode. The remaining devices operate in slave-serial mode. The PROM RESET pin is driven by INIT, and the CE input is driven by DONE. There is the potential for contention on the DONE pin, depending on the start-up sequence options chosen.

Figure 14 shows the timing of master-serial configuration. Master-serial mode is selected by a <000> or <100> on the mode pins (M2, M1, M0). Table 7 shows the timing information for Figure 13 and Figure 14.

The sequence of operations necessary to configure a BQVR300RH serially appears in Figure 15.

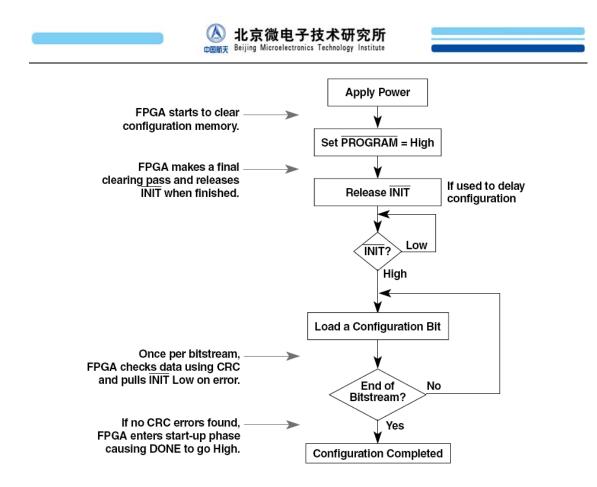


Figure 15: Serial Configuration Flowchart

4.4SelectMAP Mode

The SelectMAP mode is the fastest configuration option. Byte-wide data is written into the FPGA with a BUSY flag controlling the flow of data.

An external data source provides a byte stream, CCLK, a Chip Select (CS) signal and a Write signal (WRITE). If BUSY is asserted (High) by the FPGA, the data must be held until BUSY goes Low.

Data can also be read using the SelectMAP mode. If WRITE is not asserted, configuration data is read out of the FPGA as part of a readback operation.

In the SelectMAP mode, multiple BQVR300RH devices can be chained in parallel. DATA pins (D7:D0), CCLK, WRITE, BUSY, PROGRAM, DONE, and INIT can be connected in parallel between all the FPGAs. Note that the data is organized with the MSB of each byte on pin DO and the LSB of each byte on D7. The CS pins are kept separate, insuring that each FPGA can be selected individually. WRITE should be Low before loading the first bitstream and returned High after the last device has been programmed. Use CS to select the appropriate FPGA for loading the bitstream and sending the configuration data. at the end of the bitstream, deselect the loaded device and select the next target FPGA by setting its CS pin High. A



free-running oscillator or other externally generated signal can be used for CCLK. The BUSY signal can be ignored for frequencies below 50 MHz. BQVR300RH Configuration and Readback. Once all the devices have been programmed, the DONE pin goes High.

After configuration, the pins of the SelectMAP port can be used as additional user I/O. Alternatively, the port can be retained to permit high-speed 8-bit readback. Retention of the SelectMAP port is selectable on a design-by-design basis when the bitstream is generated. If retention is selected, PROHIBIT constraints are required to prevent the SelectMAP-port pins from being used as user I/O. Multiple BQVR300RH can be configured using the Select-MAP mode, and be made to start-up simultaneously. To configure multiple devices in this way, wire the individual CCLK, Data, WRITE, and BUSY pins of all the devices in parallel. The individual devices are loaded separately by asserting the CS pin of each device in turn and writing the appropriate data. See Table 8 for SelectMAP Write Timing Characteristics.

	Description	Value	Symbol	Value	Units
	D0-7 Setup/Hold	1/2	TSMDCC/TSMCCD	5.0 / 1.7	ns, min
	CS Setup/Hold	3/4	TSMCSCC/TSMCCCS	7.0 / 1.7	ns, min
CCLK	WRITE Setup/Hold	5/6	TSMCCW/TSMWCC	7.0 / 1.7	ns, min
	BUSY Propagation Delay	7	TSMCKBY	12.0	ns, max
	Maximum Frequency		FCC	30	MHz, max
	Maximum Frequency with no handshake		FCCNH	20	MHz, max

 Table 8: SelectMAP Write Timing Characteristics

Write

Write operations send packets of configuration data into the FPGA. The sequence of operations for a multi-cycle write operation is shown below. Note that a configuration packet can be split into many such sequences. The packet does not have to complete within one assertion of CS, illustrated in Figure 16.

- Assert WRITE and CS Low. Note that when CS is asserted on successive CCLKs, WRITE must remain either asserted or de-asserted. Otherwise an abort will be initiated, as described below.
- Drive data onto D[7:0]. Note that to avoid contention, the data source should not be enabled while CS is Low and WRITE is High. Similarly, while WRITE is High, no more that one CS should be asserted.
- 3. At the rising edge of CCLK: If BUSY is Low, the data is accepted on this clock.



If BUSY is High (from a previous write), the data is not accepted. Acceptance will instead occur on the first clock after BUSY goes Low, and the data must be held until this has happened.

- 4. Repeat steps 2 and 3 until all the data has been sent.
- 5. De-assert CS and WRITE.

A flowchart for the write operation appears in Figure 17.Note that if CCLK is slower than FCCNH, the FPGA never asserts BUSY. In this case, the above handshake is unnecessary, and data can simply be entered into the FPGA every CCLK cycle.

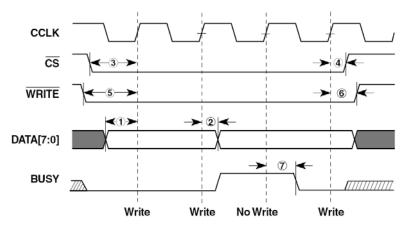


Figure 16: Write Operations

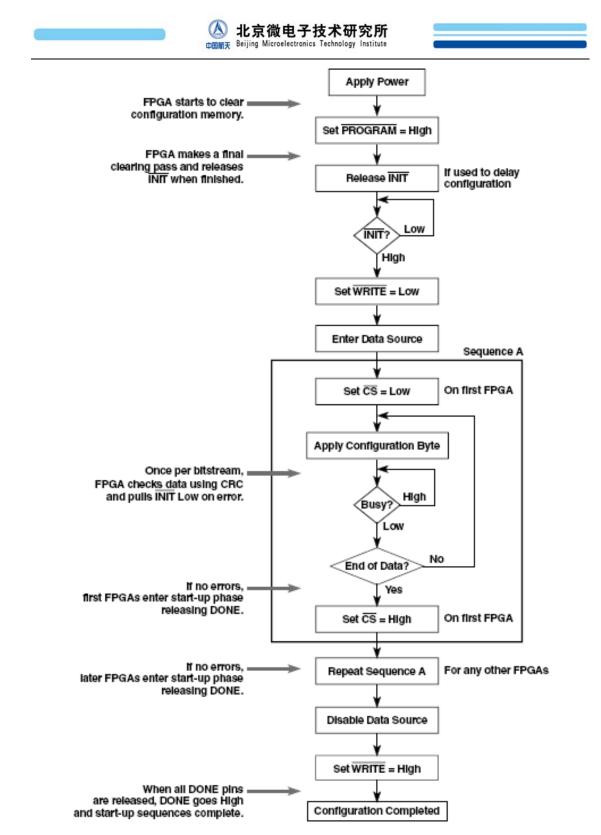


Figure 17: SelectMAP Flowchart for Write Operation

Abort

During a given assertion of CS, the user cannot switch from a write to a read, or vice-versa. This action causes the current packet command to be aborted. The device will remain BUSY until the aborted operation has completed. Following an abort, data



is assumed to be unaligned to word boundaries, and the FPGA requires a new synchronization word prior to accepting any new packets. To initiate an abort during a write operation, de-assert WRITE. At the rising edge of CCLK, an abort is initiated, as shown in Figure 18.

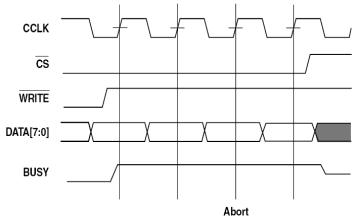


Figure 18: SelectMAP Write Abort Waveforms

4.5Boundary-Scan Mode

In the boundary-scan mode, no non-dedicated pins are required, configuration being done entirely through the IEEE 1149.1 Test Access Port.

Configuration through the TAP uses the CFG_IN instruction. This instruction allows data input on TDI to be converted into data packets for the internal configuration bus.

The following steps are required to configure the FPGA through the boundary-scan port (when using TCK as a start-up clock).

- 1. Load the CFG_IN instruction into the boundary-scan instruction register (IR)
- 2. Enter the Shift-DR (SDR) state
- 3. Shift a configuration bitstream into TDI
- 4. Return to Run-Test-Idle (RTI)
- 5. Load the JSTART instruction into IR
- 6. Enter the SDR state
- 7. Clock TCK through the startup sequence
- 8. Return to RTI Configuration and readback via the TAP is always available.

The boundary-scan mode is selected by a <101> or <001> on the mode pins (M2, M1, M0).



4.6Configuration Sequence

The configuration of BQVR300RH devices is a three-phase process. First, the configuration memory is cleared. Next, configuration data is loaded into the memory, and finally, the logic is activated by a start-up process.

Configuration is automatically initiated on power-up unless it is delayed by the user, as described below. The configuration process can also be initiated by asserting PROGRAM. The end of the memory-clearing phase is signalled by INIT going High, and the completion of the entire process is signalled by DONE going High.

The power-up timing of configuration signals is shown in Figure 19. The corresponding timing characteristics are listed in Table 9.

4.7Delaying Configuration

INIT can be held Low using an open-drain driver. An open-drain is required since INIT is a bidirectional open-drain pin that is held Low by the FPGA while the configuration memory is being cleared. Extending the time that the pin is Low causes the configuration sequencer to wait. Thus, configuration is delayed by preventing entry into the phase where data is loaded.

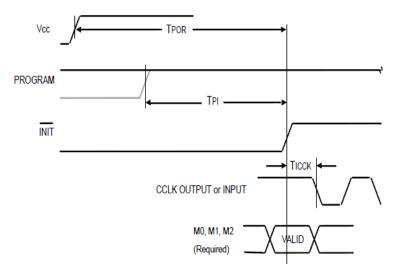


Figure 19: Power-Up Timing Configuration Signals

Description	Symbol	Value	Units
Power-on Reset	TPOR	20.0	ms,max

Table 9: Power-up Timing Characteristics

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Description	Symbol	Value	Units					
Program Latency	TPL	30.0	us,max					
CCLK (output)	TICCK	0.5	us, min					
Delay	HUCK	4.0	us, max					
Program Pulse Width	TPROGRAM	300	ns, min					

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4.8Start-Up Sequence

The default Start-up sequence is that one CCLK cycle after DONE goes High, the global 3-state signal (GTS) is released. This permits device outputs to turn on as necessary.

One CCLK cycle later, the Global Set/Reset (GSR) and Global Write Enable (GWE) signals are released. This permits the internal storage elements to begin changing state in response to the logic and the user clock.

The relative timing of these events can be changed. In addition, the GTS, GSR, and GWE events can be made dependent on the DONE pins of multiple devices all going High, forcing the devices to start in synchronism. The sequence can also be paused at any stage until lock has been achieved on any or all DLLs.

5. Electrical Characteristics

5.1DC Characteristics Absolute Maximum Ratings

Symbol	Description ⁽¹⁾		Value	Units
VCCINT	Supply voltage relative to GND ⁽²⁾		-0.5 to 3.0	V
VCCO	Supply voltage relative to GND ⁽²⁾	-0.5 to 4.0	V	
VREF	Input Reference Voltage	-0.5 to 3.6	V	
VIN	Input voltage relative to GND ⁽³⁾	3) Using VREF		V
VIIN	input voltage relative to GND	Internal threshold	-0.5 to 5.5	V
VTS	Voltage applied to 3-state output		-0.5 to 5.5	V
VCC	Longest Supply Voltage Rise Time from 1V-2.375V	50	ms	
TSTG	Storage temperature (ambient)	-65 to +150	°C	
TJ	Junction temperature	+125	°C	

Table 10: Absolute Maximum Ratings



Notes:

- 1. Stresses beyond those listed under Absolute Maximum Ratings can cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those listed under Operating Conditions is not implied. Exposure to Absolute Maximum Ratings conditions for extended periods of time can affect device reliability.
- 2. Power supplies can turn on in any order.
- 3. For protracted periods (e.g., longer than a day), VIN should not exceed VCCO by more than 3.6V.

5.2Recommended Operating Conditions

Symbol	Description	Min	Max	Units
VCCINT ⁽¹⁾	Input Supply voltage relative to GND, $TJ = -55$ °C to $+125$ °C	2.5-5%	2.5 + 5%	V
VCCO ⁽⁴⁾	Supply voltage relative to GND, $TJ = -55$ °C to $+125$ °C	1.4	3.6	V
T _{IN}	Input signal transition time		250	ns

Table 11: Recommended Operating Conditions

Notes:

- Correct operation is guaranteed with a minimum VCCINT of 2.375 V (Nominal VCCINT –5%). Below the minimum value, all delay parameters increase by 3% for each 50-mV reduction in VCCINT below the specified range.
- 2. At junction temperatures above those listed as Operating Conditions, delay parameters do increase.
- 3. Input and output measurement threshold is \sim 50% of VCC.
- 4. Min and Max values for VCCO are I/O Standard dependant.

5.3DC Characteristics Over Recommended Operating Conditions

Symbol	Description	Min	Max	Units
VIDDINT	Data Retention VCCINT Voltage (below which	2.0		V
VDRINT	configuration data can be lost)	2.0		v

Table 12: DC Characteristics Over Recommended Operating Conditions

Symbol	Description	Min	Max	Units
VDRIO	Data Retention VCCO Voltage (below which configuration data can be lost)	1.2		V
ICCINTQ	Quiescent VCCINT supply current ⁽¹⁾		250	mA
ICCOQ	Quiescent VCCO supply current ⁽¹⁾		10	mA
IREF	VREF current per VREF pin		20	μA
IL	Input or output leakage current (2)	-10	+10	μA
C _{IN}	Input capacitance (sample tested)		20	pF
IRPU	Pad pull-up (when selected) $@$ Vin = 0 V, VCCO = 3.3 V (sample tested)	Note (2)	0.25	mA
IRPD	Pad pull-down (when selected) @ Vin = 3.6 V (sample tested)	Note (2)	0.7	mA

Notes:

- With no output current loads, no active input pull-up resistors, all I/O pins 3-stated and floating.
- 2. Internal pull-up and pull-down resistors guarantee valid logic levels at unconnected input pins. These pull-up and pull-down resistors do not guarantee valid logic levels when input pins are connected to other circuits. After radiation, IL of GCLK pins and IRPD of some pins may get larger which just has tiny impact in user function.

5.4Power-On Power Supply Requirements

BQVR300RH require a certain amount of supply current during power-on to insure proper device operation. The actual current consumed depends on the power-on ramp rate of the power supply. This is the time required to reach the nominal power supply voltage of the device⁽¹⁾ from 0 V. For more information about power-on requirements see appendix II.

Product	Description ⁽²⁾	Current Requirement ^(1,3)
BQVR300RH	Minimum required current supply	2 A

Table 13: Power-On Power Supply Requirements

Notes:

^{1.} Ramp rate used for this specification is from 0 - 2.7 VDC. Peak current occurs on

or near the internal power-on reset threshold and lasts for less than 1 ms at room temperature.

- 2. Devices are guaranteed to initialize properly with the minimum current available from the power supply as noted above.
- 3. Larger currents can result if ramp rates are forced to be faster.

5.5DC Input and Output Levels

Values for VIL and VIH are recommended input voltages. Values for IOL and IOH are guaranteed output currents over the recommended operating conditions at the VOL and VOH test points. The selected standards are tested at minimum VCCO for each standard with the respective VOL and VOH voltage levels shown in table14.

Input/Output		VIL	VI	Н	VOL	VOH	IOL	IOH
Standard	V, min	V, max	V, min	V, max	V, Max	V, Min	mA	mA
LVTTL	- 0.5	0.8	2.0	5.5	0.4	2.4	24	-24
LVCMOS2	- 0.5	.7	1.7	5.5	0.4	1.9	12	-12
PCI, 3.3 V	- 0.5	44%	60%	VCCO +	10% VCCO	90% VCCO	Note 2	Note 2
1 CI, 5.5 V	- 0.5	VCCINT	VCCINT	0.5	1070 VCCO	9070 VCCO	Note 2	Note 2
PCI, 5.0 V	- 0.5	0.8	2.0	5.5	0.55	2.4	Note 2	Note 2
CTI	0.5	VDEE 0.05	VREF +	2.0	0.4	n/a	40	
GTL	- 0.5	VREF – 0.05	0.05 3.6		3.6 0.4		40	n/a
GTL+	- 0.5	VREF - 0.1	VREF + 0.1	3.6	0.6	n/a	36	n/a
HSTL I(3)	- 0.5	VREF - 0.1	VREF + 0.1	3.6	0.4	VCCO – 0.4	8	-8
HSTL III	- 0.5	VREF - 0.1	VREF + 0.1	3.6	0.4	VCCO – 0.4	24	-8
HSTL IV	- 0.5	VREF - 0.1	VREF + 0.1	3.6	0.4	VCCO – 0.4	48	-8
SSTL3 I	- 0.5	VREF - 0.2	VREF + 0.2	3.6	VREF - 0.6	VREF + 0.6	8	-8
SSTL3 II	- 0.5	VREF - 0.2	VREF + 0.2	3.6	VREF - 0.8	VREF + 0.8	16	-16
	0.5			2.0	VREF –	VREF +	7 (7 (
SSTL2 I	- 0.5	VREF – 0.2	VREF + 0.2	3.6	0.61	0.61	7.6	-7.6
	0.5			2.0	VREF –	VREF +	15.2	15.2
SSTL2 II	- 0.5	VREF – 0.2	VREF + 0.2	3.6	0.80	0.80	15.2	-15.2
CTT	- 0.5	VREF - 0.2	VREF + 0.2	3.6	VREF - 0.4	VREF + 0.4	8	-8
AGP	- 0.5	VREF - 0.2	VREF + 0.2	3.6	10% VCCO	90% VCCO	Note 2	Note 2

Table 14: DC Input and Output Levels



Notes: 1.Tested according to the relevant specifications.

6. Package Information

6.1Special Pin Definitions

Pin Name	Dedicated Pin	Direction	Description
GCK0, GCK1,	V	Input	Clock input pins that connect to Global Clock Buffers. These pins
GCK2, GCK3	Yes		become user inputs when not needed for clocks.
M0, M1, M2	Yes	Input	Mode pins are used to specify the configuration mode.
		Input or Output	The configuration Clock I/O pin: it is an input for SelectMAP and
CCLK	Yes		slave-serial modes, and output in master-serial mode. After
			configuration, it is input only, logic level = Don't Care.
PROGRAM	Yes	Input	Initiates a configuration sequence when asserted Low.
DONE	Var	Bidirectional	Indicates that configuration loading is complete, and that the
DONE	Yes		start-up sequence is in progress. The output can be open drain.
NUT	NL	Bidirectional	When Low, indicates that the configuration memory is being
11/11	INIT No		cleared. The pin becomes a user I/O after configuration.
			In SelectMAP mode, BUSY controls the rate at which configuration
	UT No		data is loaded. The pin becomes a user I/O after configuration
BUSY/ DOUT		Output	unless the SelectMAP port is retained. In bit-serial modes, DOUT
			provides header information to downstream devices in a
			daisy-chain. The pin becomes a user I/O after configuration.
D0/DIN, D1, D2,			In SelectMAP mode, D0 - D7 are configuration data pins. These
D3, D4, D5, D6,	No	Input or Output	pins become user I/Os after configuration unless the SelectMAP
D3, D4, D3, D0, D7	INO	input of Output	port is retained. In bit-serial modes, DIN is the single data input.
D7			This pin becomes a user I/O after configuration.
			In SelectMAP mode, the active-low Write Enable signal. The pin
WRITE	No	Input	becomes a user I/O after configuration unless the SelectMAP port is
			retained.
			In SelectMAP mode, the active-low Chip Select signal. The pin
CS	No	Input	becomes a user I/O after configuration unless the SelectMAP port is
			retained.

Table 15: Special Purpose Pins



Pin Name	Pin Name Dedicated Pin Direction		Description
TDI, TDO, TMS,	Yes	Mixed	Boundary-scan Test-Access-Port pins, as defined in IEEE 1149.1.
ТСК			
DXN, DXP	Yes	N/A	Temperature-sensing diode pins. (Anode: DXP, cathode: DXN)
VCCINT	Yes	Input	Power-supply pins for the internal core logic.
VCCO	Yes	Input	Power-supply pins for the output drivers (subject to banking rules)
VREF	Ne	Innut	Input threshold voltage pins. Become user I/Os when an external
VKEF	No	Input	threshold voltage is not needed (subject to banking rules).
GND	Yes	Input	Ground

6.2Pinout Information

PIN Number	PIN Name	PIN Numbe r	PIN Name	PIN Number	PIN Name	PIN Numb er	PIN Name
1	GND	58	VCCO	115	VCCO	172	TDO
2	TMS	59	M2	116	PROGRAM	173	GND
3	I/O	60	I/O	117	I/O_INIT	174	TDI
4	I/O	61	I/O	118	I/O_D7	175	I/O_CS
5	I/O_VREF_7	62	I/O	119	I/O	176	I/O_WRITE
6	I/O	63	I/O_VREF _5	120	I/O_VREF_ 3	177	I/O
7	I/O	64	I/O	121	I/O	178	I/O_VREF_ 1
8	GND	65	I/O	122	I/O	179	I/O
9	I/O_VREF_7	66	GND	123	GND	180	GND
10	I/O	67	I/O_VREF _5	124	I/O_VREF_ 3	181	I/O_VREF_ 1
11	I/O	68	I/O	125	I/O	182	I/O
12	I/O_VREF_7	69	I/O	126	I/O	183	I/O
13	I/O	70	I/O_VREF _5	127	I/O_VREF_ 3	184	I/O_VREF_ 1
14	GND	71	I/O	128	I/O_D6	185	I/O

Table 16: BQVR300RH Pinout Tables (CQFP228)

		中国航天	北京微电子 Beijing Microelectronics				
PIN Number	PIN Name	PIN Numbe r	PIN Name	PIN Number	PIN Name	PIN Numb er	PIN Name
15	VCCINT	72	GND	129	GND	186	GND
16	I/O	73	VCCINT	130	VCCINT	187	VCCINT
17	I/O	74	I/O	131	I/O_D5	188	I/O
18	VCCO	75	I/O	132	I/O	189	I/O
19	I/O	76	VCCO	133	VCCO	190	I/O
20	I/O	77	I/O	134	I/O	191	VCCO
21	I/O_VREF_7	78	I/O	135	I/O	192	I/O
22	I/O	79	I/O_VREF _5	136	I/O_VREF_ 3	193	I/O
23	I/O	80	I/O	137	I/O_D4	194	I/O_VREI 1
24	I/O	81	I/O	138	I/O	195	I/O
25	I/O	82	I/O	139	I/O	196	I/O
26	I/O_TRDY	83	VCCINT	140	VCCINT	197	I/O
27	GND	84	GCK1	141	I/O_TRDY	198	I/O
28	VCCO	85	VCCO	142	VCCO	199	GCK2
29	I/O_TRDY	86	GND	143	GND	200	GND
30	VCCINT	87	GCKO	144	I/O_IRDY	201	VCCO
31	I/O	88	I/O	145	I/O	202	GCK3
32	I/O	89	I/O	146	I/O	203	VCCINT
33	I/O	90	I/O	147	I/O	204	I/O
34	I/O_VREF_6	91	I/O	148	I/O_D3	205	I/O
35	I/O	92	I/O_VREF _4	149	I/O_VREF_ 2	206	I/O
36	I/O	93	I/O	150	I/O	207	I/O_VREI 0
37	VCCO	94	I/O	151	I/O	208	I/O
38	I/O	95	VCCO	152	VCCO	209	I/O
39	I/O	96	I/O	153	I/O	210	VCCO
40	I/O	97	I/O	154	I/O	211	I/O
41	VCCINT	98	I/O	155	I/O_D2	212	I/O

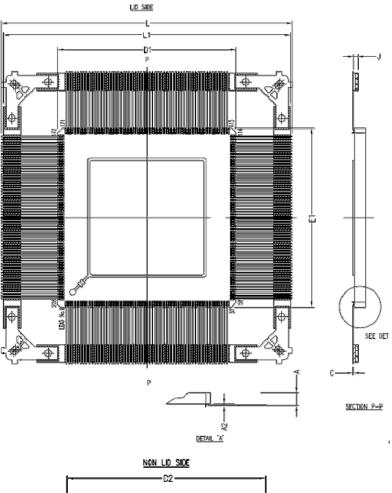
PIN Number	PIN Name	PIN Numbe r	PIN Name	PIN Number	PIN Name	PIN Numb er	PIN Name
42	GND	99	VCCINT	156	VCCINT	213	I/O
43	I/O	100	GND	157	GND	214	VCCINT
44	I/O_VREF_6	101	I/O	158	I/O_D1	215	GND
45	I/O	102	I/O_VREF _4	159	I/O_VREF_ 2	216	I/O
46	I/O	103	I/O	160	I/O	217	I/O_VREF_ 0
47	I/O_VREF_6	104	I/O	161	I/O	218	I/O
48	GND	105	I/O_VREF _4	162	I/O_VREF_ 2	219	I/O
49	I/O	106	GND	163	GND	220	I/O_VREF_ 0
50	I/O	107	I/O	164	I/O	221	GND
51	I/O_VREF_6	108	I/O	165	I/O	222	I/O
52	I/O	109	I/O_VREF _4	166	I/O_VREF_ 2	223	I/O
53	I/O	110	I/O	167	I/O	224	I/O_VREF_ 0
54	I/O	111	I/O	168	I/O_DIN_D 0	225	I/O
55	M1	112	I/O	169	I/O_DOUT _BUSY	226	I/O
56	GND	113	GND	170	CCLK	227	ТСК
57	M0	114	DONE	171	VCCO	228	VCCO

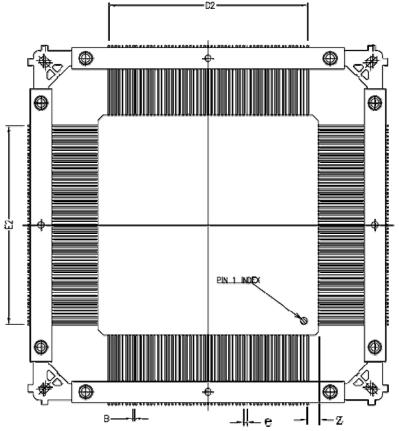
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6.3Package Outline

The outline dimensions of BQVR300RH are shown in figure 20:







Units: mm

			Ollits: Illill				
Sh al		Value					
Symbol	Min	Typical	Max				
Α	—	_	3.6				
A2	—		0.8				
В	0.17		0.30				
С	0.10		0.23				
D1/E1	38.87		39.87				
D2/E2	—	35.56					
e	0.62		0.65				
J	—	0.9					
L	—		65.50				
L1	62.99		64.26				
Ζ	_		2.5				

Figure 20: Outline Dimensions of BQVR300RH



Appendix I Electrical performance characteristics

		Conditions Limits		Lin	nits	
Test	Symbol	$2.375 \text{ V} \leq \text{VCCINT}$ $\leq 2.625 \text{ V}$ $1.2 \text{ V} \leq \text{VCCO} \leq 3.6 \text{ V}$ $(-55^{\circ}\text{C} \leq \text{TC} \leq +125^{\circ}\text{C})$	Group A Subgroups	Min	Max	units
Data retention						
VCCINT						
voltage below						
which	V _{DRINT}			2.0		V
configuration may						
be						
lost						
Data retention						
VCCO						
voltage below			1, 2, 3			
which	V _{DRIO}			1.2		V
configuration may						
be						
lost						
High-level output	V	I_{OH} =-24mA, V_{CCO} =3.0V,		2.4		V
voltage	V _{OH}	V _{CCINT} =min, LVTTL		2.4		v
Low-level output	¥7	I_{OL} =24mA, V_{CCO} =3.0V,			0.4	V
voltage	$V_{\rm OL}$	V _{CCINT} =min, LVTTL			0.4	V
Quiescent VCCINT	T				250	
Supply current	<i>I</i> _{CCINTQ}				250	mA
Quiescent VCCO	T				10	
Supply current	I _{CCOQ}				10	mA
Input or output			1, 2, 3			
leakage	$I_{ m L}$			-10	10	μΑ
current ^h						

Electrical performance characteristics

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VREF current per					
VREF	$I_{\rm REF}$			20	μΑ
pin					
Input capacitance	$C_{\rm in}/C_{\rm out}$	$f = 1.0 \text{MHz}$, $V_{\text{OUT}} = 0 \text{V}$ T c = 25 °C	4	20	pF
Pad pull-up (when selected)	$I_{ m RPU}$	$V_{\rm IN}=0$ V, $V_{\rm CCINT}=2.5$ V, $V_{\rm CCO}=3.3$ V, sample test		0.25	mA
Pad pull-down (when selected)	$I_{\rm RPD}$	$V_{\rm IN}$ =3.6V, $V_{\rm CCINT}$ =2.5V, $V_{\rm CCO}$ =3.3V, sample test	1, 2, 3	0.15	mA
Functional test	FT	$f=10$ MHz, $V_{CCINT}=2.5$ V, Vcco =3.3V	7, 8A, 8B		



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rical performance characteristic	cs - Continu	ed		
Conditions Limits		Lir	nits	
2.375 V ≤VCCINT ≤2.625 V	Group A			units
$1.2 \text{ V} \leq \text{VCCO} \leq 3.6 \text{ V}$	Subgroups	Min	Max	units

Electrical performance cha

IOB Input Switching Characteristics

(-55°C≤

Symbol

Input delays associated with the pad are specified for LVTTL levels. For other standards, adjust the delays with the values shown in "IOB Input Switching Characteristics Standard Adjustments" below this section.

 $TC \leq +125^{\circ}C)$

Propagation Delays

Test

Fropagation	Delays					
Pad to I output, no delay	$T_{ m IOPI}$				1.0	
Pad to I output, with delay	$T_{ m IOPID}$				1.9	
Pad to output IQ via transparent latch, no delay	T _{IOPLI}	2.375V≤ V_{CCINT} ≤2.625V, 1.2V≤ V_{CCO} ≤3.6V, -55°C≤ T_{A} ≤125°C	9, 10, 11		2.0	ns
Pad to output IQ via transparent latch, with delay	T _{IOPLID}				5.1	
Sequential D	Delays					
Clock CLK to output IQ	T _{IOCKIQ}	2.375V≤ V_{CCINT} ≤2.625V, 1.2V≤ V_{CCO} ≤3.6V, -55°C≤ T_A ≤125°C	9, 10, 11	_	0.8	ns
Setup and H	old Times	with respect to Clock CLK at IOB in	put register ^b	1	1	
Pad, no	T _{IOPICK} /	$2.375V \le V_{CCINT} \le 2.625V$,	9, 10, 11	2.0/0	—	ns



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delay	T _{IOICKP}	$1.2V \le V_{\rm CCO} \le 3.6V,$								
		-55℃≤ <i>T</i> _A ≤125℃								



Electi	icui perj	ormance characteristic	.s - Commu	ieu		
		Conditions Limits		Lin	nits	
		2.375 V ≤VCCINT				
	Symbo	≤2.625 V	Group A			Unit
Test	1	$1.2 \text{ V} \leq \text{VCCO} \leq 3.6$	Subgroup	Min	Max	S
	1	V	S	IVIIII	IVIAN	3
		(-55°C≤ TC				
		≤ +125°C)				
Setup and Hold Times with	h respect	to Clock CLK at IOB inj	put register ^b	ſ		
	T _{IOPICK}					
Pad, with delay	D/			5.0/0		
i uu, with ucluy	$T_{\rm IOICKP}$			5.0/0		
	D		9, 10, 11			ns
	T _{IOCEC}	$2.375V \le V_{CCINT} \le 2.625$	<i>)</i> , 10, 11			115
ICE input	к/	ν,		1.0/0		
ICL input	T _{IOCKIC}	$1.2V \le V_{\rm CCO} \le 3.6V$,		1.0/0		
	Е	-55°C≤T _A ≤125°C				
SR Input	T _{IOSRCK}					
(IFF,synchronous)	I\		9, 10, 11	1.3/0		
	T _{IOCKIS}		9, 10, 11	1.3/0		ns
	R					
Set / Reset Delays						
SR input to	T	$2.375V \le V_{CCINT} \le 2.625$	9, 10, 11		1.0	ns
IQ(asynchronous)	$T_{\rm IOSRIQ}$	ν,	9, 10, 11	_	1.8	
GSR to output IQ	T	$1.2\mathrm{V}{\leq}V_{\mathrm{CCO}}{\leq}3.6\mathrm{V},$	9, 10, 11		12.5	ns
	$T_{\rm GSRQ}$	$-55^{\circ}C \le T_A \le 125^{\circ}C$	9, 10, 11			
IOB Output Switching Cha	aracteristi	ics ^a				
Output delays terminating a	t a pad are	specified for LVTTL with	h 12 mA driv	e and fas	st slew ra	te. For
other standards, adjust the d	elays with	the values shown in "lOB	Output Swit	tching Cl	naracteris	stics
Standard Adjustments" belo	w this sec	tion.				
Propagation Delays						
O input to Pad	T _{IOOP}	$2.375V \le V_{CCINT} \le 2.625$	9, 10, 11		3.5	
1	1	1	1			1

Propagation Delays						
O input to Pad	$T_{\rm IOOP}$	$2.375V \le V_{CCINT} \le 2.625$	9, 10, 11	_	3.5	
O input to Pad via	T	ν,			4.0	ns
transparent latch	I IOOLP	$1.2V \le V_{\rm CCO} \le 3.6V,$			4.0	

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		24° 205 - 2016 - 2				
		$-55^{\circ}\text{C} \le T_{\text{A}} \le 125^{\circ}\text{C}$				
3-State Delays						
T input to Pad highimpedanc	T _{IOTHZ}			_	2.4	
T input to valid data on Pad	T _{IOTON}	0.0750 AV 2.605		_	3.7	
T input to Pad highimpedance via transparent latch	T _{IOTLPH} z	2.375V≤ V_{CCINT} ≤2.625 V, 1.2V≤ V_{CCO} ≤3.6V, -55°C≤ T_A ≤125°C	9, 10, 11		3.0	ns
T input to valid data on Pad via transparent latch	T _{IOTLPO}	$-55 C \ge T_A \ge 125 C$		_	4.2	
GTS to Pad high impedance ^c	T _{GTS}				6.3	



Electrical performance characteristics - Continued								
		Conditions Limits		Lin	nits			
		2.375 V ≤VCCINT						
Test	Symbol	≤2.625 V	Group A			Units		
Test	Symbol	$1.2 \text{ V} \leq \text{VCCO} \leq 3.6 \text{ V}$	Subgroups	Min	Max	Units		
		(-55°C≤ TC						
		≤ +125°C)						
Sequential Delays								
Clock CLK to Pad	T _{IOCKP}				3.5			
Clock CLK to Pad								
highimpedance	$T_{\rm IOCKHZ}$	$2.375V \le V_{CCINT} \le 2.625V$,			2.9			
(synchronous) ^c		$1.2V \le V_{CCO} \le 3.6V$,	9, 10, 11			ns		
Clock CLK to		-55°C≤T _A ≤125°C						
valid data on	T _{IOCKON}				4.1			
Pad (synchronous)								
Setup and Hold Tin	nes before/at	fter Clock CLK ^b						
	T _{IOOCK} /			1.2/0				
O input	T _{IOCKO}			1.3/0				
	T _{IOOCECK} /			1.0/0	_			
O OCE input	T _{IOCKOCE}		0 10 11	1.0/0				
	T _{IOSRCKO} /		9, 10, 11	1 4/0	_	ns		
SR input (OFF)	T _{IOCKOSR}	$2.375V \le V_{CCINT} \le 2.625V$,		1.4/0				
3-State Setup	T _{IOTCK} /	$1.2V \le V_{\rm CCO} \le 3.6V$,		0.0/0	_			
Times, T input	$T_{\rm IOCKT}$	-55°C≤ <i>T</i> _A ≤125°C		0.9/0				
3-State Setup	T _{IOTCECK} /			1 1 /0				
Times, TCE input	T _{IOCKTCE}			1.1/0				
3-State Setup	$T_{\rm IOSRCKT}$ /		9, 10, 11			ns		
Times, SR input	$T_{\rm IOCKTSR}$			1.3/0				
(TFF)								
Set/Reset Delays								
SR input to Pad	Т				1.0			
(asynchronous)	$T_{\rm IOSRP}$	$2.375V \le V_{\text{CCINT}} \le 2.625V$,	0 10 11	<u> </u>	4.6			
SR input to Pad	T	$1.2V \le V_{CCO} \le 3.6V$,	9, 10, 11		2.0	ns		
highimpedance	$T_{\rm IOSRHZ}$	-55°C≤T _A ≤125°C			3.9			

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(asynchronous)					
SR input to valid					
data on	T _{IOSRON}			 5.1	
Pad(asynchronous)					
Clock Distribution	Guidelines		·		
Global Clock Skew					
Global clock skew		$2.375V \le V_{CCINT} \le 2.625V$,			
between IOB	T _{GSKEWIOB}	$1.2\mathrm{V}{\leq}V_{\mathrm{CCO}}{\leq}3.6\mathrm{V},$	9, 10, 11	 0.18	ns
flip-flops ^d		-55°C≤ <i>T</i> _A ≤125°C			

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T



	ecincui pe	erformance characteristic		eu		
		Conditions Limits		Liı	nits	
		2.375 V ≤VCCINT				
Test	Symbol	≤2.625 V	Group A			Units
1051	Bymoor	$1.2 \text{ V} \leq \text{VCCO} \leq 3.6 \text{ V}$	Subgroups	Min	Max	Onits
		(-55°C≤ TC				
		≤ +125°C)				
Clock Distribution Sw	itching Cha	aracteristics GCLK IOB an	d Buffer			
Global clock pad to	<i>T</i>				0.0	
output	$T_{ m GPIO}$	$2.375V \le V_{CCINT} \le 2.625V$,		_	0.9	
Global Clock Buffer I		$1.2V \le V_{\rm CCO} \le 3.6V,$	9, 10, 11			ns
input	$T_{ m GIO}$	-55°C≤T _A ≤125°C		_	0.9	
to O output						
CLB Switching Chara	cteristics ^a					
Delays originating at F/	G inputs va	ry slightly according to the in	put used. The	e values	listed be	elow
are worst-case. Precise	values are p	rovided by the timing analyze	er.			
Combinatorial Delays						
4-input function: F/G	<i>—</i>				0.0	
inputs to X/Y outputs	$T_{\rm ILO}$			—	0.8	
5-input function: F/G						
inputs to F5 output	$T_{ m IF5}$				0.9	
5-input function: F/G						
inputs to X output	$T_{\rm IF5X}$			—	1.0	
6-input function: F/G		$2.375V \le V_{CCINT} \le 2.625V,$				
inputs to Y output via		$1.2V \le V_{CCO} \le 3.6V$,	9, 10, 11			ns
F6	$T_{\rm IF6Y}$	-55°C≤ <i>T</i> _A ≤125°C		—	1.2	
MUX						
6-input function:						
F5IN	$T_{\rm F5INY}$				0.5	
input to Y output						
BY input to YB						
output	$T_{\rm BYYB}$			—	0.7	
Setup and Hold times	before/afte	r Clock CLK ^b	1	1	1	
4-input function: F/G	$T_{\rm ICK}/T_{\rm CKI}$	$2.375V \le V_{CCINT} \le 2.625V$,	9, 10, 11		1.5/0	ns
r	iciv - UKI					

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Inputs		$1.2\mathrm{V}{\leq}V_{\mathrm{CCO}}{\leq}3.6\mathrm{V},$			
5-input function: <i>F/G</i>	T _{IF5CK} /	-55°C≤T _A ≤125°C		1.7/0	
inputs	$T_{\rm CKIF5}$			1.7/0	
6-input function:	T				
F5IN	$T_{\rm F5INCK}$		—	1.2/0	
input	T _{CKF5IN}				
6-input function: F/G	T _{IF6CK}			1.9/0	
inputs via F6 MUX	$T_{\rm CKIF6}$			1.9/0	



Electrical performance characteristics - Continued												
		Conditions Limits		Lir	nits							
		2.375 V ≤VCCINT										
Test	Symbol	≤2.625 V	Group A			Units						
1051	Symbol	$1.2 \text{ V} \leq \text{VCCO} \leq 3.6 \text{ V}$	Subgroups	Min	Max	Units						
		(-55°C≤ TC										
		≤ +125°C)										
Setup and Hold times	before/after	r Clock CLK ^b										
BX/BY inputs	$T_{\rm DICK}/$				0.8/0							
DA/D1 inputs	$T_{\rm CKDI}$	2 2751/21 -2 (251)			0.8/0							
CE innut	T _{CECK} /	$2.375V \le V_{\text{CCINT}} \le 2.625V$,	9, 10, 11		1.0/0							
CE input	$T_{\rm CKCE}$	$1.2V \le V_{CCO} \le 3.6V$,	9, 10, 11	_	1.0/0	ns						
SR/BY inputs	Т	-55°C≤T _A ≤125°C			0.0/0							
(synchronous)	T _{RCKTCKR}				0.9/0							
CLOCK CLK												
Minimum Pulse	T				2.0							
Width, High	T _{CH}	$2.375V \le V_{CCINT} \le 2.625V$,	0 10 11		2.0							
Minimum Pulse	T	$1.2V \le V_{CCO} \le 3.6V$,	9, 10, 11		2.0	ns						
Width, Low	$T_{\rm CL}$	$-55^{\circ}\text{C} \le T_{\text{A}} \le 125^{\circ}\text{C}$			2.0							
Set/Reset												
Minimum Pulse												
Width,	T_{RPW}				3.3							
SR/BY inputs												
Delay from SR/BY												
inputs to XQ/YQ	T.	$2.375V \le V_{CCINT} \le 2.625V$,	0 10 11		1.4							
outputs	$T_{ m RQ}$	$1.2V \le V_{\rm CCO} \le 3.6V$,	9, 10, 11	—	1.4	ns						
(asynchronous)		-55°C≤T _A ≤125°C										
Delay from GSR to												
XQ/YQ	T _{IOGSRQ}				12.5							
outputs												
CLB Arithmetic Switc	hing Chara	ecteristics ^a		1		1						
Setup times not listed ex	xnlicitly can	be approximated by decreasi	ing the combi	natorial	Setup times not listed explicitly can be approximated by decreasing the combinatorial delays by the							

Setup times not listed explicitly can be approximated by decreasing the combinatorial delays by the setup time adjustment listed. Precise values are provided by the timing analyzer.

Combinatorial Delays

		北京微电子技术研究所 _{表 Beijing Microelectronics Technology Institute}				
F operand inputs to X						
via	$T_{\rm OPX}$			—	1.0	
XOR						
F operand input to XB	T _{OPXB}				1.4	
output	I OPXB				1.7	
F operand input to Y						
via	$T_{\rm OPY}$			—	2.0	
XOR		$2.375V \le V_{CCINT} \le 2.625V$,				
F operand input to YB	$T_{\rm OPYB}$	$1.2V \le V_{\rm CCO} \le 3.6V$,	9, 10, 11		2.0	ns
output	TOPIB	$-55^{\circ}C \le T_{A} \le 125^{\circ}C$	<i>y</i> , 10, 11		2.0	115
F operand input to		55 C <u>1</u> <u>A</u> 125 C				
COUT	$T_{\rm OPCYF}$				1.5	
output						
G operand inputs to Y						
via	$T_{\rm OPGY}$			—	1.2	
XOR						
G operand input to	T _{OPGYB}				2.1	
YB output	4 OPGAR				2.1	



		Conditions Limits	- Continu	Lir	nits	
Test	Symbo 1	$2.375 \text{ V} \leq \text{VCCINT}$ $\leq 2.625 \text{ V}$ $1.2 \text{ V} \leq \text{ VCCO} \leq 3.6$ V $(-55^{\circ}\text{C} \leq \text{ TC}$ $\leq +125^{\circ}\text{C})$	Group A Subgrou ps	Min	Max	Units
G operand input to COUT output	T _{OPCYG}				1.6	
BX initialization input to COUT	T _{BXCY}		9, 10, 11		1.1	ns
CIN input to X output via XOR	T _{CINX}	$2.375V \le V_{CCINT} \le 2.625V$			0.6	
ClN input to XB	T _{CINXB}	$1.2V \le V_{CCO} \le 3.6V$,			0.1	
CIN input to Y via XOR	<i>T</i> _{CINY}	$- 55^{\circ} \mathbb{C} \leq T_{A} \leq 125^{\circ} \mathbb{C}$	9, 10, 11		0.6	ns
ClN input to YB	T _{CINYB}			_	0.6	
CIN input to COUT output	$T_{ m BYP}$			_	0.2	
Multiplier Operation						
F1/2 operand inputs to XB output via AND	T _{FANDX} B				0.5	
F1/2 operand inputs to YB output via AND	T _{FANDY} B			_	1.1	
F1/2 operand inputs to COUT output via AND	T _{FANDC}	$2.375V \le V_{CCINT} \le 2.625V$	9, 10,		0.6	ns
G1/2 operand inputs to YB output via AND	T _{GANDY} в	$1.2V \le V_{CCO} \le 3.6V,$ $-55^{\circ}C \le T_A \le 125^{\circ}C$	11	_	0.7	
G1/2 operand inputs to COUT output via AND	T _{GANDC}				0.2	
Setup and Hold Times befo	ore/after (Clock CLK ^b				
CIN input to FFX	$T_{\rm CCKX}/$ $T_{\rm CKCX}$	$2.375V \le V_{CCINT} \le 2.625V$	9, 10, 11		1.3/0	ns



CIN input to FFY	T _{CCKY} /	$1.2\mathrm{V}{\leq}V_{\mathrm{CCO}}{\leq}3.6\mathrm{V},$		1.4/0	
	T _{CKCY}	$-55^{\circ}C \le T_{A} \le 125^{\circ}C$		1.4/0	



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stics - Co	ntinued		

$ \begin{array}{c c c c c c c c c c c c c c c c c c c $		-		1	1		
$ \begin{array}{ c c c c c } Test & Symbol & Symbol & Subprime \\ \hline Symbol & Symbol & Symbol & Subprime \\ \hline State \\ \hline State \\ \hline State \\ \hline State \\ \hline Symbol & Subprime \\ \hline Subprime \\ \hline State \\ \hline State \\ \hline Subprime \\ \hline Symbol & Subprim \\ \hline Symbol & Subprime \\ \hline Symbol & $			Conditions Limits		Lir	nits	
Test Symbol $1.2 V \le VCCO \le 3.6 V$ (-55°C $\le TC$ $\le +125°C) Subgroups Min Max s CLB SelectRAM Switching Characteristics"Sequential Delays CLOK CLK to X/Youtputs(WE active)Clock CLK to X/Youtputs 7_{SHCKO} 2.375V \le V_{CCINT} \le 2.625V, \\ 1.2V \le V_{CCO} \le 3.6V, \\ -55 C \le T_A \le 125 C 9, 10, 10, 10, 10, 10, 10, 10, 10, 10, 10$			2.375 V ≤VCCINT	Group			
$\begin{array}{ c c c c c } & 1.2 \ V \leq \ VCCO \leq 3.6 \ V \\ (.55^{\circ}C \leq \ TC \\ \leq \ +125^{\circ}C) \end{array} & ups \end{array} & Min & Max & s \\ \hline \\ \mbox{Min} & Max & s \\ \hline \\ \mbox{CLS belectRAM Switching Characteristics} \\ \hline \\ \mbox{Sequential Delays} \\ \hline \\ \mbox{Clock CLK to X/Y} & \\ \mbox{outputs} & T_{SHCKO} & 2.375 \ V \leq V_{CCNT} \leq 2.625 \ V, \\ 1.2 \ V \leq V_{CCO} \leq 3.6 \ V, \\ .55 \ C \leq T_A \leq 125 \ C \\ \hline \\ \mbox{Min} & 10 & 11 & - \\ \hline \\ \mbox{Setup and Hold Times before/after Clock CLK^b} \\ \hline \\ \mbox{F/G address inputs} & T_{As/T_{AH}} & \\ \mbox{Dist} T_{DS/T_{D11}} & 2.375 \ V \leq V_{CCNT} \leq 2.625 \ V, \\ 1.2 \ V \leq V_{CCO} \leq 3.6 \ V, \\ .55 \ C \leq T_A \leq 125 \ C \\ \hline \\ \mbox{Min} & Mode \\ \hline \\ \mbox{BX/BY data inputs} & T_{DS/T_{D11}} & \\ \mbox{T}_{DS/T_{D11}} & T_{SHOCK} & 2.375 \ V \leq V_{CCNT} \leq 2.625 \ V, \\ 1.2 \ V \leq V_{CCO} \leq 3.6 \ V, \\ .55 \ C \leq T_A \leq 125 \ C \\ \hline \\ \mbox{Dist} & T_{SHOCK} & 2.375 \ V \leq V_{CCNT} \leq 2.625 \ V, \\ 1.2 \ V \leq V_{CCO} \leq 3.6 \ V, \\ .55 \ C \leq T_A \leq 125 \ C \\ \hline \\ \mbox{Min} & Mode \\ \hline \\ \mbox{BX/BY data inputs} & T_{SHOCK} & 2.375 \ V \leq V_{CCNT} \leq 2.625 \ V, \\ 1.2 \ V \leq V_{CCO} \leq 3.6 \ V, \\ .55 \ C \leq T_A \leq 125 \ C \\ \hline \\ \mbox{Min} & Mode \\ \hline \\ \mbox{BX/BY data inputs} & T_{SHOCK} & 2.375 \ V \leq V_{CCNT} \leq 2.625 \ V, \\ 1.2 \ V \leq V_{CCO} \leq 3.6 \ V, \\ .55 \ C \leq T_A \leq 125 \ C \\ \hline \\ \mbox{Min} & Min \\ \mbox{Min} & Pulse \\ \hline \\ \mbox{Widh, Low} & T_{MPH} \\ \hline \\ \mbox{Minimum Pulse} & T_{WPH} \\ \hline \\ \mbox{Minimum clock} \\ \mbox{period to meet} \\ \mbox{address write cycle} \\ \mbox{T}_{WC} & 2.375 \ V \leq V_{CCNT} \leq 2.625 \ V, \\ .55 \ C \leq T_A \leq 125 \ C \\ \hline \\ \mbox{Minimum Pulse} & T_{WC} \\ \hline \\ \mbox{Minimum Pulse} \\ \hline \\ Minimum Pulse$	Test	Symbol	≤2.625 V	Α			Unit
$ \begin{array}{ c c c c c c } \hline \begin{tabular}{ c c c c } \hline \begin{tabular}{ c c c c } \hline \begin{tabular}{ c c } \hline \hline \begin{tabular}{ c c } \hline \begin{tabular}{ c c } \hline \begin{tabular}{ c c } \hline \beg$	Test	Symbol	$1.2 \text{ V} \leq \text{VCCO} \leq 3.6 \text{ V}$	Subgro	Min	Max	S
CLB SelectRAM Switching Characteristics* Sequential Delays Clock CLK to X/Y $2.375V \le V_{CCINT} \le 2.625V$, $1.2V \le V_{CCOS} 3.6V$, $55 \ T \le T_A \le 125 \ T \ T \ T \ 125 \ T \ T \ T \ T \ 125 \ T \ T \ T \ 125 \ T \ T \ T \ T \ T \ T \ T \ T \ T \ $			(-55°C≤ TC	ups			
Sequential Delays Clock CLK to X/Y outputs(WE active) 2.375V $\leq V_{CCINT} \leq 2.625V$, $1.2V \leq V_{CCO} \leq 3.6V$, $-55^{\circ} C \leq T_A \leq 125^{\circ} C$ 9, 10, 11 - 3.0 ns Setup and Hold Times before/after Clock CLK ^b F/G address inputs T_{AS}/T_{AH} 2.375V $\leq V_{CCINT} \leq 2.625V$, $1.2V \leq V_{CCO} \leq 3.6V$, $1.2V \leq V_{CCO} \leq 3.6V$, 1.1 $0.7/0$ $-$ ns BX/BY data inputs (DIN) T_{MS}/T_{MH} $2.375V \leq V_{CCINT} \leq 2.625V$, $1.2V \leq V_{CCO} \leq 3.6V$, $-55^{\circ} C \leq T_A \leq 125^{\circ}C$ $9, 10, 10$, 11 $0.9/0$ $-$ ns Shift Register Mode BX/BY data inputs (DIN) T_{SHDICK} $2.375V \leq V_{CCINT} \leq 2.625V$, $1.2V \leq V_{CCO} \leq 3.6V$, $-55^{\circ} C \leq T_A \leq 125^{\circ}C$ $9, 10, 11$ 0.9 $ ns$ Minimum Pulse Width, Low T_{WPL} $2.375V \leq V_{CCINT} \leq 2.625V$, $1.2V \leq V_{CCO} \leq 3.6V$, $-55^{\circ} C \leq T_A \leq 125^{\circ}C$ $9, 10, 11$ 3.1 $ a.5$ Width, Low T_{WPL} $2.375V \leq V_{CCINT} \leq 2.625V$, $1.2V \leq V_{CCO} \leq 3.6V$, $-55^{\circ} C \leq T_A \leq 125^{\circ}C$ $9, 10, 11$ 3.1 $ a.5$ Shift Regist			≤ +125°C)				
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	CLB SelectRAM Swit	tching Chara	cteristics ^a				
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	Sequential Delays						
$ \begin{array}{ c c c c c c } \hline \mbox{Outputs} (WE active) \\ \hline \mbox{Clock CLK to X/Y} \\ \hline \mbox{Outputs} & T_{SHCKO} & 1.2V \leq V_{CCO} \leq 3.6V, \\ -55^{\circ}C \leq T_A \leq 125^{\circ}C & 11 & & 3.0 \\ \hline \mbox{Setup and Hold Times before/after Clock CLK^b} \\ \hline \mbox{Setup and Hold Times before/after Clock CLK^b} \\ \hline \mbox{Setup and Hold Times before/after Clock CLK^b} \\ \hline \mbox{Setup and Hold Times before/after Clock CLK^b} \\ \hline \mbox{Setup and Hold Times before/after Clock CLK^b} \\ \hline \mbox{Setup and Hold Times before/after Clock CLK^b} \\ \hline Support of the transformation of transformation of the transformation of transforma$	Clock CLK to X/Y					2.0	
$ \begin{array}{ c c c c c c } \hline Clock CLK to X/Y \\ outputs & & & & & & & & & & & & & & & & & & &$	outputs(WE active)			9, 10,	-	3.0	
outputs Image: constraint of the sector of th	Clock CLK to X/Y	T _{SHCKO}		11			ns
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	outputs		$-55^{\circ}\text{C} \leq T_{\text{A}} \leq 125^{\circ}\text{C}$		—	3.0	
BX/BY data inputs (DIN) T_{DS}/T_{DH} $2.375V \le V_{CCINT} \le 2.625V$, $1.2V \le V_{CCO} \le 3.6V$, $-55 °C \le T_A \le 125 °C$ 9, 10, 11 $0.9/0$ — ns Shift Register Mode T_{WS}/T_{WH} $2.375V \le V_{CCINT} \le 2.625V$, $1.2V \le V_{CCO} \le 3.6V$, $-55 °C \le T_A \le 125 °C$ 9, 10, 11 $0.9/0$ — ns Shift Register Mode T_{SHDICK} $2.375V \le V_{CCINT} \le 2.625V$, $1.2V \le V_{CCO} \le 3.6V$, $-55 °C \le T_A \le 125 °C$ 9, 10, 11 0.9 — ns CE input (WS) T_{SHCECK} $2.375V \le V_{CCINT} \le 2.625V$, $-55 °C \le T_A \le 125 °C$ 9, 10, 11 0.9 — ns Minimum Pulse width, High T_{WPH} $2.375V \le V_{CCINT} \le 2.625V$, $1.2V \le V_{CCO} \le 3.6V$, $-55 °C \le T_A \le 125 °C$ 9, 10, 11 3.1 — ns Minimum Pulse address write cycle time T_{WC} $2.375V \le V_{CCINT} \le 2.625V$, $-55 °C \le T_A \le 125 °C$ 9, 10, 11 6.2 — ns Shift Register Mode T_{WC} $2.375V \le V_{CCINT} \le 2.625V$, $-55 °C \le T_A \le 125 °C$ 9, 10, 3.1 3.1 — ns	Setup and Hold Time	s before/after	r Clock CLK ^b	I			
$\begin{array}{c c c c c c c c c c c c c c c c c c c $	F/G address inputs	$T_{\rm AS}/T_{\rm AH}$			0.7/0		
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	BX/BY data inputs			9, 10,	0.0/0		
CE input (WE) T_{WS}/T_{WH} 1.0/0 - Shift Register Mode BX/BY data inputs (DIN) T_{SHDICK} 2.375V $\leq V_{CCINT} \leq 2.625V$, $1.2V \leq V_{CCO} \leq 3.6V$, $-55°C \leq T_A \leq 125°C$ 9, 10, 11 0.9 - ns CE input (WS) T_{SHCECK} $2.375V \leq V_{CCINT} \leq 2.625V$, $-55°C \leq T_A \leq 125°C$ 9, 10, 11 1.0 - ns Minimum Pulse T_{WPH} $2.375V \leq V_{CCINT} \leq 2.625V$, $1.2V \leq V_{CCO} \leq 3.6V$, $-55°C \leq T_A \leq 125°C$ 3.1 - ns Minimum clock period to meet address write cycle time T_{WC} $2.375V \leq V_{CCINT} \leq 2.625V$, $-55°C \leq T_A \leq 125°C$ 6.2 - ns Shift Register Mode T_{WC} $2.375V \leq V_{CCINT} \leq 2.625V$, 9, 10, 3.1 - ns	(DIN)	$T_{\rm DS}/T_{\rm DH}$		11	0.9/0		ns
BX/BY data inputs (DIN) T_{SHDICK} $2.375V \le V_{CCINT} \le 2.625V$, $1.2V \le V_{CCO} \le 3.6V$, $-55°C \le T_A \le 125°C$ 9, 10, 11 0.9 — ns Clock CLKMinimum Width, High T_{WPH} $2.375V \le V_{CCINT} \le 2.625V$, $1.2V \le V_{CCO} \le 3.6V$, $-55°C \le T_A \le 125°C$ 9, 10, 11 3.1 —Minimum Width, High T_{WPH} $2.375V \le V_{CCINT} \le 2.625V$, $1.2V \le V_{CCO} \le 3.6V$, $-55°C \le T_A \le 125°C$ 3.1 —Minimum Pulse Width, Low T_{WPL} $2.375V \le V_{CCINT} \le 2.625V$, $1.2V \le V_{CCO} \le 3.6V$, $-55°C \le T_A \le 125°C$ $9,$ 10, 11 3.1 —Minimum clock period to meet address write cycle time T_{WC} $2.375V \le V_{CCINT} \le 2.625V$, $9,$ 10, 3.1 $9,$ 10, 3.1 $-$ Shift Register Mode T_{SRPH} $2.375V \le V_{CCINT} \le 2.625V$, $9,$ 10, 3.1 $9,$ 10, 3.1 $-$	CE input (WE)	$T_{\rm WS}/T_{\rm WH}$	$-55^{\circ}\text{C} \le T_{\text{A}} \le 125^{\circ}\text{C}$		1.0/0		
(DIN) T_{SHDICK} $1.2V \le V_{CCO} \le 3.6V$, $-55^{\circ}C \le T_A \le 125^{\circ}C$ 9, 10, 11 0.9 — ns CE input (WS) T_{SHCECK} T_{SHCECK} $2.55^{\circ}C \le T_A \le 125^{\circ}C$ 9, 10, 11 1.0 — ns Clock CLK Minimum Pulse T_{WPH} $2.375V \le V_{CCINT} \le 2.625V$, $Midth, Low$ 3.1 — 3.1 — ns Minimum Pulse T_{WPL} $2.375V \le V_{CCINT} \le 2.625V$, $1.2V \le V_{CCO} \le 3.6V$, $-55^{\circ}C \le T_A \le 125^{\circ}C$ $9, 10, 10, 10, 10, 10, 10, 10, 10, 10, 10$	Shift Register Mode	I	I				
$\begin{array}{c c c c c c c c c c c c c c c c c c c $	BX/BY data inputs		$2.375V \le V_{CCINT} \le 2.625V$,				
CE input (WS) T_{SHCECK} $-55^{\circ}C \le T_A \le 125^{\circ}C$ 1.0 $-$ Clock CLKMinimumPulseWidth, High T_{WPH} MinimumPulseMinimumPulseWidth, Low T_{WPL} $2.375V \le V_{CCINT} \le 2.625V$, $1.2V \le V_{CCO} \le 3.6V$, $-55^{\circ}C \le T_A \le 125^{\circ}C$ 9, 10, 3.1 9, 10, 11 6.2 $ 6.2$ $ Minimum$ Pulse T_{WC} $2.375V \le V_{CCINT} \le 2.625V$, $-55^{\circ}C \le T_A \le 125^{\circ}C$ 6.2 $ 6.2$ $ 6.2$ $ 6.2$ $ 6.2$ $ Minimum$ Pulse T_{SRPH} $2.375V \le V_{CCINT} \le 2.625V$, $9, 10, 3.19, 10, 3.1 0, 10, 0.10.10, 10, 0.10.10, 10, 0.10.10, 10, 0.10.10, 10, 0.10.10, 10, 0.10.10, 10, 0.10.10, 10, 0.10.10, 10, 0.10.10, 10, 0.10.1$	(DIN)	T_{SHDICK}	$1.2V \le V_{CCO} \le 3.6V$,		0.9		ns
Minimum Width, HighPulse T_{WPH} T_{WPH} $2.375V \le V_{CCINT} \le 2.625V$, $1.2V \le V_{CCO} \le 3.6V$, $-55^{\circ}C \le T_A \le 125^{\circ}C$ 3.1 $-$ Minimum Width, Low T_{WPL} $2.375V \le V_{CCINT} \le 2.625V$, $1.2V \le V_{CCO} \le 3.6V$, 	CE input (WS)	T _{SHCECK}	-55°C≤T _A ≤125°C	11	1.0		
Width, High T_{WPH} 3.1 $-$ MinimumPulse T_{WPL} $2.375V \le V_{CCINT} \le 2.625V$, $1.2V \le V_{CCO} \le 3.6V$, $-55 °C \le T_A \le 125 °C$ $9, 10, 11$ 3.1 $-$ Minimum clock period to meet address write cycle time T_{WC} T_{WC} $55°C \le T_A \le 125°C$ 6.2 $-$ Shift Register ModeMinimumPulse T_{SRPH} $2.375V \le V_{CCINT} \le 2.625V$, $9, 10, 3.1$ 3.1 $-$ ns	Clock CLK	I					
Width, HighImage: MinimumPulse T_{WPL} $2.375V \le V_{CCINT} \le 2.625V$, $1.2V \le V_{CCO} \le 3.6V$, $-55 °C \le T_A \le 125 °C$ 9, 10, 11 3.1 Image: Minimum 3.1 Image: Minimum $address write cycleT_{WC}T_{WC}2.375V \le V_{CCINT} \le 2.625V,-55 °C \le T_A \le 125 °C9, 10,113.1Image: Minimumaddressaddress write cycleT_{WC}2.375V \le V_{CCINT} \le 2.625V,9, 10,9, 10,3.13.1Image: MinimumMinimumMinimumMinimumMinimumMinimumMinimum2.375V \le V_{CCINT} \le 2.625V,9, 10,9, 10,3.13.1Image: Minimum$	Minimum Pulse	T			2.1		
Width, Low T_{WPL} $2.375V \le V_{CCINT} \le 2.625V$, $1.2V \le V_{CCO} \le 3.6V$, $-55°C \le T_A \le 125°C$ 9, 10, 11 3.1 —nsMinimum clock period to meet address write cycle time T_{WC} $-55°C \le T_A \le 125°C$ $9, 10, 11$ 6.2 — 6.2 —Shift Register Mode T_{WC} $2.375V \le V_{CCINT} \le 2.625V$, $9, 10, 3.1$ —ns	Width, High	$T_{\rm WPH}$			3.1		
Width, Low1.2V $\leq V_{CCO} \leq 3.6V$, -55°C $\leq T_A \leq 125$ °C9, 10, 11nsMinimum clock period to meet address write cycle time T_{WC} 1.2V $\leq V_{CCO} \leq 3.6V$, -55°C $\leq T_A \leq 125$ °C116.2Shift Register ModeMinimum Pulse T_{SRPH} 2.375V $\leq V_{CCINT} \leq 2.625V$, $2.625V$,9, 10, 3.1 3.1ns	Minimum Pulse	_					
Minimum clock period to meet address write cycle time T_{WC} $-55^{\circ}C \le T_A \le 125^{\circ}C$ 116.2—Shift Register ModeShift Register Mode2.375V \le V_{CCINT} \le 2.625V, 9, 10, 3.1—ns	Width, Low	$T_{ m WPL}$		9, 10,	3.1		
period to meet address write cycle time T_{WC} 6.2 $-$ Shift Register Mode2.375V $\leq V_{CCINT} \leq 2.625V$,9, 10, 3.1 $-$ ns	Minimum clock			11			ns
address write cycle timeImage: Second systemImage: Second systemShift Register Mode2.375V $\leq V_{CCINT} \leq 2.625V$, 9, 10, 3.1 — nsMinimumPulse T_{SRPH} 2.375V $\leq V_{CCINT} \leq 2.625V$, 9, 10, 3.1 — ns	period to meet		$-55 \cup \le I_A \le 125 \cup$				
Shift Register ModeMinimumPulse $2.375V \le V_{CCINT} \le 2.625V$,9, 10, 3.1 —ns	address write cycle	$T_{\rm WC}$			6.2		
Minimum Pulse $2.375V \le V_{CCINT} \le 2.625V$, 9, 10, 3.1 — ns	time						
T_{SRPH} 3.1 — ns	Shift Register Mode	1					
I_{SRPH}	Minimum Pulse	Т	$2.375V \le V_{CCINT} \le 2.625V$,	9, 10,	2 1		 -
Width, High $1.2V \le V_{CCO} \le 3.6V$, 11	Width, High	1 SRPH	$1.2V \le V_{CCO} \le 3.6V$,	11	5.1		ns

	中国航天	北京微电子技术研究所 Beijing Microelectronics Technology Institute				
Minimum Pulse Width, Low	$T_{ m SRPL}$	-55°C≤T _A ≤125°C		3.1	_	
Block RAM Switching Sequential Delays	g Characteris	stics ^a				
Clock CLK to DOUT output	T _{BCKO}	$2.375V \le V_{CCINT} \le 2.625V,$ $1.2V \le V_{CCO} \le 3.6V,$ $-55^{\circ}C \le T_{A} \le 125^{\circ}C$	9, 10, 11		4.1	ns



$ \begin{array}{ c c c c c } \mbox{Test} & \mbox{Limits} \\ \mbox{Symbol} & \mbox{Limits} \\ 2.375 V \leq VCCINT \\ \leq 2.625 V \\ 1.2 V \leq VCCO \\ \leq 3.6 V \\ (-55°C \leq TC \\ \leq +125°C) \end{array} & \mbox{Limits} \\ \mbox{Subgrou} \\ Subgrou$	El	eciricai perje	ormance characterist	ucs - Coni	inuea		
Test Symbol $\leq 2.625 V$ $1.2 V \leq VCCO\leq 3.6 V(-55°C \leq TC\leq +125°C) Group ASubgroups Am Max Units ADDR inputs T_{BACK/BCKA}DIN inputs T_{BACK/BCKA}T_{BDCK/BCKO} 2.375V \leq V_{CCINT} \leq 2.625V,1.2V \leq V_{CCO} \leq 3.6V,-55°C \leq TA \leq 125°C) 9, 10, 10, 10, 10, 10, 10, 10, 10, 10, 10$			Conditions Limits		Lir	nits	
Test Symbol $1.2 \vee \leq VCCO$ Subgrou Min Max Units Setup and Hold Times betweet of $(-55^{\circ}C \leq TC)$ $\leq +125^{\circ}C$) $= +125^{\circ}C$) $= +125^{\circ}C$			2.375 V ≤VCCINT				
$ \begin{array}{ c c c c c } & & & & & & & & & & & & & & & & & & &$			≤2.625 V	Group A			
$ \begin{array}{ c c c c c } & & & & & & & & & & & & & & & & & & &$	Test	Symbol	$1.2 V \le VCCO$	Subgrou	N.C.	M	Units
Setup and Hold Times \vdash +125°C) I. I. I. ADDR inputs $T_{BACK/BCKA}$ 2.375V $\leq V_{CCINT} \leq 2.6$ 9, 10, 11 1.5/0 - DIN inputs $T_{BACK/BCKA}$ 2.375V $\leq V_{CCINT} \leq 2.6$ 9, 10, 11 3.4/0 - RST input $T_{BRCK/BCKA}$ $2.5\nabla, 5$ $2.5\nabla, 5$ $3.4/0$ - WEN input $T_{BRCK/BCKA}$ $5^{5}\nabla \leq T_A \leq 125^{\circ}$ C $3.0/0$ - Minimum Pulse Width, High T_{BPWH} $2.375V \leq V_{CCINT} \leq 2.6$ $5^{5}\nabla, 5^{-1}A \leq 125^{\circ}$ C 1.0^{-1} $3.0/0$ - Minimum Pulse Width, High T_{BPWH} $2.375V \leq V_{CCINT} \leq 2.6$ $5^{5}\nabla, 5^{-1}A \leq 125^{\circ}$ C 1.0^{-1}			≤3.6 V	ps	Min	Max	
Setup and Hold Times before/after Clock CLK ^b ADDR inputs $T_{BACK/BCKA}$ $2.375V \le V_{CCINT} \le 2.6$ $1.5/0$ $-$ DIN inputs $T_{BDCK/BCKD}$ $2.375V \le V_{CCINT} \le 2.6$ $2.5V$, $1.5/0$ $-$ RST input $T_{BRCK/BCKR}$ $2.375V \le V_{CCINT} \le 2.6$ $3.4/0$ $ 3.2/0$ $-$ WEN input $T_{BRCK/BCKR}$ $-55^{\circ}C \le T_A \le 125^{\circ}C$ $3.0/0$ $ 3.0/0$ $-$ Clock CLK T_{BPWHI} $2.375V \le V_{CCINT} \le 2.6$ $2.5V$, 1.1 2.0 $ ns$ Minimum Pulse Width, High T_{BPWHI} $2.375V \le V_{CCINT} \le 2.6$ $2.5V$, 1.1 2.0 $ ns$ Minimum Pulse Width, High T_{BPWII} $2.375V \le V_{CCINT} \le 2.6$ $2.5V$, 1.1 4.0 $ ns$ TBCF Switching Characteristics Combinatorial Delays In input to OUT output ⁴ T_{O} $1.2V \le V_{CCO} \le 3.6V$, $9.10,$ 10.2 $ 1.5$ 0.2 $ 1.5$			(-55°C≤ TC				
$ \begin{array}{ c c c c c } \hline ADDR inputs & $T_{BACK/BCKA}$ \\ \hline DIN inputs & $T_{BDCK/BCKD}$ \\ \hline DIN input & $T_{BDCK/BCKR}$ \\ \hline RST input & $T_{BBCK/BCKR}$ \\ \hline RST input & $T_{BBCK/BCKR}$ \\ \hline RST input & $T_{BBCK/BCKR}$ \\ \hline Minimum Pulse Width, T_{BWVL} & $-55^{\circ}C \leq T_A \leq 125^{\circ}C$ \\ \hline 1.2V \leq V_{CCDS} \leq 3.6V, $-55^{\circ}C \leq T_A \leq 125^{\circ}C$ \\ \hline 1.2V \leq V_{CCDS} \leq 3.6V, $-55^{\circ}C \leq T_A \leq 125^{\circ}C$ \\ \hline Minimum Pulse Width, T_{BPWL} \\ \hline High & T_{BPWL} \\ \hline Cuck CLK & $CLKB setup time T_{BCCS} \\ \hline CLKA & CLKB setup time T_{BCCS} \\ \hline TBUF Switching Characteristics \\ \hline TBUF Switching Characteristics \\ \hline TRU input to OUT output^a T_{IO} \\ \hline TRI input to OUT output T_{OFF} \\ \hline TRI input to valid data on T_{ON} \\ \hline TAG Test Access Port Switching Characteristics \\ \hline TMS and TDI Setup times T_{TAPTCK} \\ \hline TMS and TDI Setup times T_{TAPTCK} \\ \hline TAG Test Access Port Switching Characteristics \\ \hline TMS and TDI Setup times T_{TAPTCK} \\ \hline Tag Setup times T_{TAPTCK} \\ \hline TAG Test Access Port Switching Characteristics \\ \hline TMS and TDI Setup times T_{TAPTCK} \\ \hline TAG Test Access Port Switching Characteristics \\ \hline TMS and TDI Setup times T_{TAPTCK} \\ \hline Tag Setup times T_{TAPTCK} \\ \hline TAG Test Access Port Switching Characteristics \\ \hline TMS and TDI Setup times T_{TAPTCK} \\ \hline TAG Test Access Port Switching Characteristics \\ \hline TMS and TDI Setup times T_{TAPTCK} \\ \hline TAG Test Access Port Switching Characteristics \\ \hline TMS and TDI Setup times T_{TAPTCK} \\ \hline TMS and TDI Setup times \\ \hline TAG Test Access Port Switching Characteristics \\ \hline TMS and TDI Setup times \\ \hline TAG Test Access Port Switching Characteristics \\ \hline TMS and TDI Setup times \\ \hline TAG Test Access Port Switching Characteristics \\ \hline TMS and TDI Setup time \\ \hline TAG Test Access Port Switching Characteristics \\ \hline TMS and TDI Setup time \\ \hline TAG Test Access Port Switching Characteristics \\ \hline TMS and TDI Setup time \\ \hline TAG Test Access Port Switching Characteristics \\ \hline TMS and TDI Setup \\ \hline TAG Test Access Port Switching Characterist $-55^{\circ}C S = S_{TA} S = S_{TA} S \\ \hline T$			≤ +125°C)				
$ \begin{array}{ c c c c c } \hline \text{DIN inputs} & $T_{\text{BDCK/BCKD}} \\ \hline \text{DIN input} & $T_{\text{BDCK/BCKR}} \\ \hline \text{EN input} & $T_{\text{BBCK/BCKR}} \\ \hline \text{RST input} & $T_{\text{BBCK/BCKR}} \\ \hline \text{RST input} & $T_{\text{BBCK/BCKR}} \\ \hline \text{WEN input} & $T_{\text{BWCK/BCKW}} \\ \hline \end{tabular} \\ \hline \text{WEN input} & $T_{\text{BWCK/BCKW}} \\ \hline \end{tabular} \\ \hline \text{WeN input} & $T_{\text{BWCK/BCKW}} \\ \hline \end{tabular} \\ \hline \e$	Setup and Hold Times be	efore/after Clo	ck CLK ^b				
$ \begin{array}{ c c c c } \hline \text{DIN inputs} & $T_{\text{BDCK/BCKD}} \\ \hline \text{EN input} & $T_{\text{BECK/BCKR}} \\ \hline \text{EN input} & $T_{\text{BECK/BCKR}} \\ \hline \text{RST input} & $T_{\text{BRCK/BCKR}} \\ \hline \text{WEN input} & $T_{\text{BWCK/BCKR}} \\ \hline \text{Minimum Pulse Width,} \\ \text{High} & $T_{\text{BPWH}} \\ \\ \text{Low} & $T_{\text{BPWL}} \\ \hline \text{CLKA CLKB setup} \\ \text{time} & $T_{\text{BCCS}} \\ \hline \text{for different ports} \\ \hline \text{TBUF Switching Characeiristics} \\ \hline \text{TBUF Switching Characeiristics} \\ \hline \text{TRI input to OUT output}^{d} & $T_{\text{IO}} \\ \hline \text{TRI input to OUT output}^{d} \\ \hline \text{for of } $T_{\text{OFF}} \\ \hline \text{IN input to valid data} \\ \text{on} & $T_{\text{ON}} \\ \hline \text{OUT output}^{d} \\ \hline \text{OUT output}^{d} \\ \hline \text{ON} \\ \hline \text{TAG Test Access Port Strictsing Characeiristics} \\ \hline \begin{array}{c} 2.375V \leq V_{\text{CCNT}} \leq 2.6 \\ 25V, \\ 1.2V \leq V_{\text{COS}} \leq 3.6V, \\ 1.2V \leq 0.6V \leq 3.6V, \\ 1.1V \leq 3.6V \leq 3.6V \\ 1.1V = 10 \\ 1.1V = 10 \\ 1.1V = 10 \\ 1.1V = 10 \\ 1$	ADDR inputs	T _{BACK/BCKA}	2 2751/20 2 (1.5/0	—	
$ \begin{array}{ c c c c } \hline {\rm EN \ input} & $T_{\rm BECK/BCKR} \\ \hline {\rm RST \ input} & $T_{\rm BRCK/BCKW} \\ \hline {\rm RST \ input} & $T_{\rm BRCK/BCKW} \\ \hline {\rm WEN \ input} & $T_{\rm BWCK/BCKW} \\ \hline {\rm WEN \ input} & $T_{\rm BWCK/BCKW} \\ \hline {\rm WEN \ input} & $T_{\rm BWCK/BCKW} \\ \hline {\rm Minimum \ Pulse \ Width, \\ High \\ \hline {\rm High} & $T_{\rm BPWH} \\ \\ Low & $CLKA \ CLKB \ setup \\ time \\ for different ports \\ \hline {\rm CDek \ CLK} \\ \hline {\rm CLKA \ CLKB \ setup \\ time \\ for different ports \\ \hline {\rm TBUF \ Switching \ Characes \ Input \ Court output^a \\ \hline {\rm RST \ input \ to \ OUT \ output^a \\ high-impedance^a \\ on \\ on \\ OUT \ output^a \\ \hline {\rm TGN \ court $	DIN inputs	T _{BDCK/BCKD}		0 10	1.5/0		
$\begin{array}{ c c c c c } \hline RST input & $T_{BRCK/BCKR}$ & $-55 \ensuremath{\mathbb{C}} \le $T_A \le 125 \ensuremath{\mathbb{C}} & $3.0'0$ & $-$$ \\ \hline \hline $3.0'0$ & $-$ \\ \hline \hline \hline $3.0'0$ & $-$ \\ \hline $	EN input	T _{BECK/BCKE}			3.4/0		ns
$ \begin{array}{ c c c c } WEN input & T_{BWCK/BCKW} & & & & & & & & & & & & & & & & & & &$	RST input	T _{BRCK/BCKR}		11	3.2/0	_	
$\begin{array}{c c c c c c c c c } \mbox{Minimum Pulse Width,} & $T_{\rm BPWH}$ & $T_{\rm BPWH}$ & $2.375 V \le V_{\rm CCINT} \le 2.6$ & $25V$, $1.2V \le V_{\rm CCOS} \le 3.6V$, $-55 \ C \le T_{\rm A} \le 125 \ C \ & 11 & 4.0 & $-$ & & $-$ & & $-$ & $$	WEN input	T _{BWCK/BCKW}			3.0/0	—	
$\begin{array}{c c c c c c c } & $T_{\rm BPWH}$ & $T_{\rm BPWH}$ & $T_{\rm BPWL}$ & $2.375V \le V_{\rm CCINT} \le 2.6$ \\ $25V,$ & $25V,$ & $1.2V \le V_{\rm CCOS} \le 3.6V,$ & $1.1V \le V_{\rm CCOS} \le 3.6V,$ & $1.2V \le V_{\rm CCOS} \le 0.6V,$ & $1.2V \le V_{\rm COS} \le 0.6V,$ & $1.2V \le V_{\rm COS} \le 0.6V,$ & $1.2V \le V_{\rm COS} \le 0.6V,$ & $1.2V \le 0.6V \le 0.6V,$ & $1.2V \le 0.6V \le 0.6V \le 0.6V,$ & $1.2V \le 0.6V \le 0.$	Clock CLK	•		•			
HighIntra 2.375V $\leq V_{CCINT} \leq 2.6$ 25V, 1.2V $\leq V_{CCO} \leq 3.6V$, 1.2V $\leq V_{CCO} \leq 3.6V$, 1.2V $\leq V_{CCO} \leq 3.6V$, 1.1I.0II	Minimum Pulse Width,	T			2.0		
$\begin{array}{ c c c c c } \hline \mbox{Minimum Pulse Width,} & T_{BPWL} & $25V,$ & $9,$10,$ & 2.0 & $-$$\\ \hline \mbox{CLKA CLKB setup} & $$$$$$$$$$$$$$$$$$$$$$$$$$$$$$$$$$$$	High				2.0		
$\begin{array}{c c c c c c c c c c c c c c c c c c c $	Minimum Pulse Width,				2.0		1
CLKA CLKB setup time T_{BCCS} $-55^{\circ}C \le T_A \le 125^{\circ}C$ 4.0 for different ports 4.0 4.0 TBUF Switching Characteristics Combinatorial Delays IN input to OUT output ^a T_{IO} A_{IO} TRI input to OUT output ^a T_{OFF} $2.375V \le V_{CCINT} \le 2.6$ $9, 10, 10, 10.2$ TRI input to valid data T_{ON} $1.2V \le V_{CCO} \le 3.6V, 11.0$ 0.2 OUT output ^a T_{ON} $-55^{\circ}C \le T_A \le 125^{\circ}C$ 0.2 JTAG Test Access Port Sutching Characteristics T_{TAPTCK} $2.375V \le V_{CCINT} \le 2.6$ $9, 10, 11$ 4.0 ns	Low	I BPWL			2.0		ns
time for different ports T_{BCCS} 4.0for different portsTBUF Switching CharacteristicsCombinatorial DelaysIN input to OUT outputa T_{IO} $-$ TRI input to OUT output T_{OFF} $2.375V \le V_{CCINT} \le 2.6$ $25V,$ $9, 10,$ 0.2 $-$ TRI input to valid data on OUT outputa T_{ON} $1.2V \le V_{CCO} \le 3.6V,$ $-55 °C \le T_A \le 125 °C$ 0.2 $ ns$ THAG Test Access Port Switching CharacteristicsTMS and TDI Setup times T_{TAPTCK} $2.375V \le V_{CCINT} \le 2.6$ $25V,$ $9, 10,$ 11 4.0 $ ns$	CLKA CLKB setup			11			
TBUF Switching CharacteristicsCombinatorial DelaysIN input to OUT outputa T_{IO} IN input to OUT output T_{OFF} $high-impedance^a$ T_{OFF} $TRI input to valid dataT_{ON}1.2V \le V_{CCO} \le 3.6V,9, 10, 110.20.30.40.40.50.50.50.50.50.50.5$	time	$T_{ m BCCS}$	$-55 \cup \le I_A \le 125 \cup$		4.0	—	
Combinatorial DelaysIN input to OUT outputa T_{IO} I_{IO} I_{OFF} $2.375V \le V_{CCINT} \le 2.6$ $25V$, 9, 10, 11 0.2 $$ TRI input to Valid data on OUT outputa T_{ON} $1.2V \le V_{CCO} \le 3.6V$, 11 0.2 $$ TAG Test Access Port Switching Characteristics $2.375V \le V_{CCINT} \le 2.6$ $25V$, 9, 10, 11 0.2 $$ TMS and TDI Setup times T_{TAPTCK} $2.375V \le V_{CCINT} \le 2.6$ $25V$, 9, 10, 11 $9, 10, 10, 11$ 4.0 $$	for different ports						
$ \begin{array}{c c c c c c c c c } \hline \text{IN input to OUT output}^{a} & T_{10} & $&&&&&&&&&&&&&&&&&&&&&&&&&&&&&&&&&$	TBUF Switching Charac	teristics					
TRI input to OUT output high-impedancea T_{OFF} $2.375V \le V_{CCINT} \le 2.6$ $25V$, $1.2V \le V_{CCO} \le 3.6V$, $-55 °C \le T_A \le 125 °C$ 0.2 $-$ TRI input to valid data on OUT outputa T_{ON} $1.2V \le V_{CCO} \le 3.6V$, $-55 °C \le T_A \le 125 °C$ 11 0.2 $-$ JTAG Test Access Port Switching Characteristics TMS and TDI Setup times T_{TAPTCK} $2.375V \le V_{CCINT} \le 2.6$ $25V$, $9, 10, 11$ 4.0 $-$ ns	Combinatorial Delays						
high-impedance ^a T_{OFF} $25V$, $1.2V \le V_{CCO} \le 3.6V$, $-55 °C \le T_A \le 125 °C$ 9, 10, 11 0.2 $-$ TRI input to valid data on OUT output ^a T_{ON} $1.2V \le V_{CCO} \le 3.6V$, $-55 °C \le T_A \le 125 °C$ $9, 10,$ 11 0.2 $ ns$ JTAG Test Access Port Switching CharacteristicsTMS and TDI Setup times T_{TAPTCK} $2.375V \le V_{CCINT} \le 2.6$ $25V,$ $9, 10,$ 11 4.0 $ ns$	IN input to OUT output ^a	T _{IO}			0		
high-impedancea25V,9, 10,nsTRI input to valid data on OUT outputa T_{ON} $1.2V \le V_{CCO} \le 3.6V,$ $-55 °C \le T_A \le 125 °C$ 11 0.2 JTAG Test Access Port Switching CharacteristicsTMS and TDI Setup times T_{TAPTCK} $2.375V \le V_{CCINT} \le 2.6$ $25V,$ 9, 10, 11 4.0	TRI input to OUT output	T	$2.375V \le V_{CCINT} \le 2.6$		0.2		
TRI input to valid data on OUT outputa T_{ON} $1.2V \le V_{CCO} \le 3.6V$, $-55 °C \le T_A \le 125 °C$ 11 0.2 0.2 $-$ JTAG Test Access Port Switching Characteristics $2.375V \le V_{CCINT} \le 2.6$ $25V$, $9, 10, 11$ 4.0 $-$ ns	high-impedance ^a	I OFF	25V,	9, 10,	0.2		
OUT outputaImage: CharacteristicsJTAG Test Access Port Switching CharacteristicsTMS and TDI Setup times $2.375V \le V_{CCINT} \le 2.6$ $25V$,9, 10, 114.0—ns	TRI input to valid data		$1.2V \le V_{\rm CCO} \le 3.6V,$	11			ns
JTAG Test Access Port Switching CharacteristicsTMS and TDI Setup times $2.375V \le V_{CCINT} \le 2.6$ $25V$,9, 10, 114.0—ns	on	$T_{ m ON}$	$-55^{\circ}C \le T_A \le 125^{\circ}C$		0.2		
TMS and TDI Setup $2.375V \le V_{CCINT} \le 2.6$ 9, 10, 4.0 — ns times T_{TAPTCK} $25V$, 11 4.0 — ns	OUT output ^a						
times T_{TAPTCK} 25V, $\begin{pmatrix} 9, 10, \\ 11 \\ 11 \\ \end{pmatrix}$ 4.0 — ns	JTAG Test Access Port S	witching Cha	racteristics	•			
times T_{TAPTCK} 25V, 11 4.0 — ns	TMS and TDI Setup		$2.375V \le V_{CCINT} \le 2.6$	0 10			
	times	T _{TAPTCK}	25V,		4.0	_	ns
	before TCK ^a		$1.2\mathrm{V}{\leq}V_{\mathrm{CCO}}{\leq}3.6\mathrm{V},$	11			

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TMS and TDI Hold		-55°C≤ <i>T</i> _A ≤125°C				
times	$T_{\rm CKTAP}$			2.0	—	
after TCK ^a						
Output delay from clock	Т				11.0	
TCK to output TDO ^g	T_{TCKDO}				11.0	
Maximum TCK clock	E				22	MIIa
frequency ^g	F _{TCK}				33	MHz



	20	een teut performanee enaraetern	lites com	innea		
		Conditions Limits	Group A	Li	mits	
Test	Symbol	2.375 V ≤VCCINT ≤2.625 V	Subgroup			Uni
1051	Symbol	$1.2 \text{ V} \leq \text{VCCO} \leq 3.6 \text{ V}$		Min	Max	ts
		$(-55^{\circ}C \leq TC \leq +125^{\circ}C)$	S			
Pin-to-Pin Inp	out Paramet	ter Guidelines				
Global Clock	Input to Ou	utput Delay for LVTTL, 12 mA, Fa	st Slew Rate	, with D	LL	
LVTTL-F12 ^g	T _{ICKOFDL}	$2.375V \le V_{CCINT} \le 2.625V$,	0 10 11		2.0	
	L	$1.2\mathrm{V}{\leq}V_{\mathrm{CCO}}{\leq}3.6\mathrm{V},$	9, 10, 11		3.6	ns
LVTTL-F12 ^g	T _{ICKOFF}	-55℃≤ <i>T</i> A≤125℃	9, 10, 11		5.9	ns
Minimum Clo	ock to Ou			Min	imum	
I/OStandard				With	Witho	
				DLL	ut	
					DLL	
LVTTL-S2 ^{a e}	_			5.2	6.1	
LVTTL-S4 ^{ae}	_			3.5	4.4	
LVTTL-S6 ^{ae}	_			2.8	3.7	1
LVTTL-S8 ^{ae}				2.2	3.1	•
LVTTL-S12 ^a	_			2.0	2.9	
e				2.0	2.9	
LVTTL-S16 ^a	—			1.9	2.8	
e				1.9	2.0	_
LVTTL-S24 ^a	—	$2.375V \le V_{CCINT} \le 2.625V$,		1.8	2.7	
e		$1.2V \le V_{\rm CCO} \le 3.6V$,	9, 10,	1.0	2.7	ns
LVTTL-F2 ^{ae}	_	$-55^{\circ}C \le T_{A} \le 125^{\circ}C$	11	2.9	3.8	115
LVTTL-F4 ^{ae}	—			1.7	2.6	_
LVTTL-F6 ^{ae}	_			1.2	2.1	
LVTTL-F8 ^{ae}	—			1.1	2.0	
LVTTL-F12 ^a	_			1.0	1.9	
e				1.0	1.7	
LVTTL-F16 ^a	_			0.9	1.8	
e				0.9	1.0	
LVTTL-F24 a				0.9	1.0	
e					1.8	



LVCMOS2 ^a	_		1.1	2.0	
PCI33-3 ^a			1.5	2.4	
PCI33-5 ^a			1.4	2.3	
PCI66-3 ^a			1.1	2.0	
GTL ^a			1.6	2.5	
GTL+ ^a	_		1.7	2.6	
HSTL I ^a	_		1.1	2.0	
HSTL III ^a			0.9	1.8	
HSTL IV ^a			0.8	1.7	
SSTL2 I ^a			0.9	1.8	
SSTL2 II ^a			0.8	1.7	
SSTL3 I ^a	_		0.8	1.7	
SSTL3 II ^a	—		0.7	1.6	
CTT ^a			1.0	1.9	
AGP ^a			1.0	1.9	



		Conditions Limits 2.375 V ≤VCCINT		Li	mits	
Test	Symbol	$\leq 2.625 \text{ V}$ $1.2 \text{ V} \leq \text{ VCCO} \leq 3.6 \text{ V}$ $(-55^{\circ}\text{C} \leq \text{ TC}$ $\leq +125^{\circ}\text{C})$	Group A Subgroup s	Min	Max	Units
Pin-to-Pin Input Para	meter Guide	lines ^g				
Global Clock Set-Up	and Hold for	LVTTL Standard, with D	OLL			
Input Setup and Hold	Time Relative	to Global Clock Input Sign	al for LVTT	L Standa	ard. For d	ata
input with different sta	ndards,adjust	the setup time delay by the	values shown	n in Inpu	ıt Delay	
Adjustments						
No Delay, Global Clock and IFF, with DLL	$T_{ m PSDLL}/T_{ m PH}$ dll	$2.375V \le V_{CCINT} \le 2.625V$		2.1/- 0.4	_	
Full Delay, Global Clock and IFF, without DLL	T _{PSFD} /T _{PHF} D	$1.2V \le V_{CCO} \le 3.6V,$ $-55^{\circ}C \le T_A \le 125^{\circ}C$	9, 10, 11	3.1/ 0.0	_	ns
DLL Timing Parame	ters ⁱ			11		
Input Clock Frequency (CLKDLLHF) ^f	F _{CLKINHF}			60	180	
Input Clock Frequency (CLKDLL) ^f	F _{CLKINLF}	$2.375V \le V_{CCINT} \le 2.625V$, $1.2V \le V_{CCO} \le 3.6V$,	9, 10, 11	25	90	MHz
Input Clock Pulse Width(CLKDLLHF) ^a	T _{DLLPWHF}	-55°C≤T _A ≤125°C		2.4	_	ns
Input Clock Pulse Width (CLKDLL) ^a	$T_{ m DLLPWLF}$			3.0	_	115
CLKDLLHF ^a	T		1	1		ſ
Input Clock Period Tolerance	$T_{ m IPTOL}$	$2.375V \le V_{\text{CCINT}} \le 2.625V$			1.0	ns
Input Clock Jitter (Cycle to Cycle)	T _{IJITCC}	1.2V≤ V_{CCO} ≤3.6V, -55°C≤ T_A ≤125°C	9, 10, 11		±150	ps
Time Required for	T _{LOCK}	$f_{\rm CLKIN}$ >60MHz			20	μs

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DLL to Acquire Lock					
DLL Output skew					
(between any DLL	$T_{\rm SKEW}$			 ±150	ps
output)		$2.375V \le V_{CCINT} \le 2.625V$			
DLL Output long		,			
term phase	$T_{\rm OPHASE}$	$1.2V \le V_{\rm CCO} \le 3.6V,$		 ±100	ps
differential		$-55^{\circ}C \le T_{A} \le 125^{\circ}C$			
DLL Output jitter	Т				
cycle to cycle	$T_{\rm OJITCC}$			±60	ps



		Conditions Limits 2.375 V ≤VCCINT ≤2.625 V	Group A	Limits		
Test	Symbol	$1.2 \text{ V} \leq \text{VCCO} \leq 3.6 \text{ V}$ $(-55^{\circ}\text{C} \leq \text{TC} \leq +125^{\circ}\text{C})$	Subgroup s	Min	Max	Units
CLKDLL ^a						
Input Clock						
Period	$T_{\rm IPTOL}$	$2.375V \le V_{CCINT} \le 2.625V$,			1.0	ns
Tolerance		$1.2\mathrm{V}{\leq}V_{\mathrm{CCO}}{\leq}3.6\mathrm{V},$	9, 10, 11			
Input Clock Jitter	Т	-55°C≤T _A ≤125°C			±300	20
(Cycle to Cycle)	T _{IJITCC}				±300	ps
Time Required for						
DLL to Acquire	$T_{\rm LOCK}$	$f_{\rm CLKIN} > 60 {\rm MHz}$		—	20	μs
Lock						
DLL Output skew						
(between any	$T_{\rm SKEW}$			—	±150	
DLL output)		$2.375V \le V_{CCINT} \le 2.625V$,	9, 10, 11			
DLL Output long		$1.2V \le V_{CCO} \le 3.6V,$				ng
term phase	T _{OPHASE}	$-55^{\circ}\mathbb{C} \le T_{A} \le 125^{\circ}\mathbb{C}$		—	±100	ps
differential		$-33 \cup \underline{-1}_{A} \underline{-1}23 \cup$				
DLL Output jitter	T _{OJITCC}				±60	
cycle to cycle	¹ OJITCC				-00	

a The parameter is design guaranteed and should not included in qualification test.

b A Zero "0" Hold Time listing indicates no hold time or a negative hold time. Negative values can not be guaranteed "best-case", however, if a "0" is listed, there is no positive hold time.

c 3-state turn-off delays should not be adjusted.

d These clock-skew delays are provided for guidance only. They reflect the delays encountered in a typical design under worst-case conditions. Precise values for a particular design are provided by the timing analyzer.

e S= Slow Slew Rate, F= Fast Slew Rate

f The parameter should included in qualification test.

g The parameter isn't test now because current test condition can't meet the accuracy demand, if

the test condition is improved and can cover the test accuracy, the parameter should be test.

h Special pins or multifunction pins may not included in qualification test.

After Total Ionizing Dose test the max lockable frequency may decrease by 5%.

Appendix II Application Notes

• Master CCLK Frequency

In Master Serial configuration mode, the CCLK frequency driven by BQVR300RH is correlated to the OSCFSEL-Specified Master CCLK Frequencies set by the ISE design suit. The actual Master CCLK Frequency is much smaller than the setting value. For example, when the ISE-set Master CCLK frequency is 60MHz, the practical Master CCLK Frequency driven by BQVR300RH is about 24MHz. Because of the structures of the internal oscillators, master CCLK frequency is accurate to $\pm 45\%$, and so is Xilinx XQVR300. If the configuration time matters for designer, the master CCLK Frequency deviation should be considered, for more information refer to appendix IV.

• Initialization

In the setup process, INIT_B is internally driven Low during initialization, then released after T_{POR} . The release time of Initial depends on the internal oscillators of FPGA. The T_{POR} of BQVR300RH is 10ms – 20ms, which is larger than XQVR300.

• Power Matching and Power-on Circuit

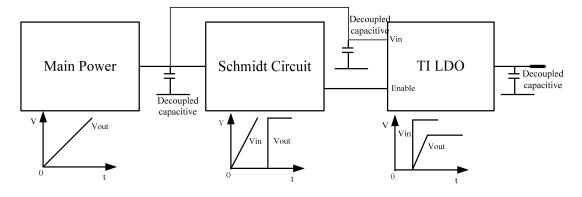
The Power-On Surge is the current that an SRAM-based FPGA draws upon first applying power. When the FPGA powers up, but before initialization, the RAM cells are briefly in a random state, which results in the POS current draw during power-on. All SRAM-based FPGAs require a minimum supply current to ensure a successful power up. The POS current is very large in size, but only lasts a short period of time (usually on the order of milliseconds). The POS current is related to junction temperatures. As a result, power adaptability tests at whole temperature ranges are required during initial stage of design.

The power-on current can be significant for high performance FPGAs, particularly since they employ extensive buffering for fast signal switching and propagation. During power-up, this buffering creates additional current paths between power and ground. Most FPGA manufactures publish power-on current specifications. The POS specification of BQVR300RH guarantees successful power-on when the following conditions are met: (1) The VCCINT power supply has the ability to continuously output 2A current and should only be used for one FPGA; (2) The VCCINT rise time should be less than 1ms; (3) VCCINT rises steadily from GND to



2.5V (no negative dips in the voltage, no shelf in power-on voltage profile); (4) PCB-level power adaptability tests at whole temperature ranges are required during initial stage of design.

The figure below shows a reference design in which a schmidt circuit is used to delay the LDO enable signal till the LDO's input voltage is enough high. The value of decoupled capacitance should be chosen carefully if the capacitance is too large the VCCINT rise time may exceed the required value.





Appendix III Common Mistakes

• DONE pin

Example: some users once connected a $4.7K\Omega$ pull up resistor to DONE pin, as a result BQVR300RH failed in startup sequence and had no function even the DONE pin was high.

Pull up resistor connected to Done pin must be 330Ω otherwise the device may not startup successfully. If the pull up resistor connected to Done pin is not available in PCB, an alternative solution is to choose "drive done pin high" or "enable internal done pipe" in startup options of ISE.

• CS pin and Write pin

Example: some users thought the CS pin and the Write pin was useless in none-SelectMAP mode, and connected those two pins with uncertain logic state, but the master serial mode configuration was failed for the uncertain state of the CS pin and the Write pin.

Under any configuration mode cs pin and write pin should tied to a constant logic otherwise the configuration may fail. Users may think cs and write are useless if the configuration mode isn't SelectMAP mode. Be attention that even if not in SelectMAP mode the logic changes in cs pin and write pin may cause the device shut down during the configuration.

• DLL reset and locked signal

Example: some users didn't wait for the DLL being locked, as a result the initial disordered clocks made their function abnormal.

The RST pin, active High, must either connect to a dynamic signal or tied to ground. As the DLL delay taps reset to zero, glitches can occur on the DLL clock output pins. Activation of the RST pin can also severely affect the duty cycle of the clock output pins. Furthermore, the DLL output clocks no longer de-skew with respect to one another. For these reasons, rarely use the reset pin unless reconfiguring the device or changing the input frequency.

In order to achieve lock, the DLL may need to sample several thousand clock cycles. Do not use the DLL output clock signals until after activation of the LOCKED signal. Prior to the activation of the LOCKED signal, the DLL output clocks are not

valid and can exhibit glitches, spikes, or other spurious movement.

• Initializing reset

Example: some users reset their BQVR300RH function after power on, but the reset signal was disabled before the DONE pin went high, as a result the function was not really reset.

Configuration costs a period of time, during the process BQVR300RH has no function. If the design need a initializing reset, please make sure the reset is active after the DONE pin goes high which indicates that the configuration is finished.

Appendix IV Master CCLK Frequency for Reference Only

OCCESEI	ISE-set Master CCLK	practical Master CCLK Frequency
OSCFSEL	frequency (MHz)	(MHz)
101101	60	24.4
110100	55	17.9
101010	51	19.6
110011	45	14.1
100111	41	14.3
110010	34	10.3
011101	30	12.2
011010	26	9.7
010111	20	7.1
001101	15	6
001010	13	4.85
000111	10	3.58
000110	9.2	3.15
000101	8.1	2.69
000100	6.9	2.23
010001	5.4	1.56
000010	4	1.28
000000	2.5	0.778



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